16-bit Proprietary Microcontroller

F²MC-16FX MB96630 Series

MB96F633R/A, MB96F635R/A, MB96F636R, MB96F637R

■ DESCRIPTION

MB96630 series is based on FUJITSU's advanced F^2MC -16FX architecture (16-bit with instruction pipeline for RISC-like performance). The CPU uses the same instruction set as the established F^2MC -16LX family thus allowing for easy migration of F^2MC -16LX Software to the new F^2MC -16FX products. F^2MC -16FX product improvements compared to the previous generation include significantly improved performance - even at the same operation frequency, reduced power consumption and faster start-up time.

For high processing speed at optimized power consumption an internal PLL can be selected to supply the CPU with up to 32MHz operation frequency from an external 4MHz to 8MHz resonator. The result is a minimum instruction cycle time of 31.2ns going together with excellent EMI behavior. The emitted power is minimized by the on-chip voltage regulator that reduces the internal CPU voltage. A flexible clock tree allows selecting suitable operation frequencies for peripheral resources independent of the CPU speed.

Note: F²MC is the abbreviation of FUJITSU Flexible Microcontroller.

FUJITSU SEMICONDUCTOR provides information facilitating product development via the following website. The website contains information useful for customers.

http://edevice.fujitsu.com/micom/en-support/



■ FEATURES

Technology

0.18µm CMOS

• CPU

- F²MC-16FX CPU
- Optimized instruction set for controller applications (bit, byte, word and long-word data types, 23 different addressing modes, barrel shift, variety of pointers)
- 8-byte instruction queue
- Signed multiply (16-bit × 16-bit) and divide (32-bit/16-bit) instructions available

System clock

- \bullet On-chip PLL clock multiplier (×1 to ×8, ×1 when PLL stop)
- 4MHz to 8MHz crystal oscillator (maximum frequency when using ceramic resonator depends on Q-factor)
- Up to 8MHz external clock for devices with fast clock input feature
- 32.768kHz subsystem quartz clock
- 100kHz/2MHz internal RC clock for quick and safe startup, clock stop detection function, watchdog
- Clock source selectable from mainclock oscillator, subclock oscillator and on-chip RC oscillator, independently for CPU and 2 clock domains of peripherals
- The subclock oscillator is enabled by the Boot ROM program controlled by a configuration marker after a Power or External reset
- Low Power Consumption 13 operating modes (different Run, Sleep, Timer, Stop modes)

On-chip voltage regulator

Internal voltage regulator supports a wide MCU supply voltage range (Min=2.7V), offering low power consumption

• Low voltage detection function

Reset is generated when supply voltage falls below programmable reference voltage

Code Security

Protects Flash Memory content from unintended read-out

• DMA

Automatic transfer function independent of CPU, can be assigned freely to resources

Interrupts

- Fast Interrupt processing
- 8 programmable priority levels
- Non-Maskable Interrupt (NMI)

CAN

- Supports CAN protocol version 2.0 part A and B
- ISO16845 certified
- Bit rates up to 1Mbps
- 32 message objects
- Each message object has its own identifier mask
- Programmable FIFO mode (concatenation of message objects)
- Maskable interrupt
- Disabled Automatic Retransmission mode for Time Triggered CAN applications
- Programmable loop-back mode for self-test operation

• USART

- Full duplex USARTs (SCI/LIN)
- Wide range of baud rate settings using a dedicated reload timer
- Special synchronous options for adapting to different synchronous serial protocols
- LIN functionality working either as master or slave LIN device
- Extended support for LIN-Protocol to reduce interrupt load

• I²C

- Up to 400kbps
- Master and Slave functionality, 7-bit and 10-bit addressing

• A/D converter

- SAR-type
- 8/10-bit resolution
- Signals interrupt on conversion end, single conversion mode, continuous conversion mode, stop conversion mode, activation by software, external trigger, reload timers and PPGs
- Range Comparator Function
- Scan Disable Function

• Source Clock Timers

Three independent clock timers (23-bit RC clock timer, 23-bit Main clock timer, 17-bit Sub clock timer)

Hardware Watchdog Timer

- Hardware watchdog timer is active after reset
- Window function of Watchdog Timer is used to select the lower window limit of the watchdog interval

Reload Timers

- 16-bit wide
- Prescaler with $1/2^1$, $1/2^2$, $1/2^3$, $1/2^4$, $1/2^5$, $1/2^6$ of peripheral clock frequency
- Event count function

Free-Running Timers

- Signals an interrupt on overflow, supports timer clear upon match with Output Compare (0, 4)
- Prescaler with 1, $1/2^1$, $1/2^2$, $1/2^3$, $1/2^4$, $1/2^5$, $1/2^6$, $1/2^7$, $1/2^8$ of peripheral clock frequency

• Input Capture Units

- 16-bit wide
- Signals an interrupt upon external event
- Rising edge, Falling edge or Both (rising & falling) edges sensitive

Output Compare Units

- 16-bit wide
- Signals an interrupt when a match with Free-running Timer occurs
- A pair of compare registers can be used to generate an output signal

Programmable Pulse Generator

- 16-bit down counter, cycle and duty setting registers
- Can be used as 2 × 8-bit PPG
- Interrupt at trigger, counter borrow and/or duty match
- PWM operation and one-shot operation
- Internal prescaler allows 1, 1/4, 1/16, 1/64 of peripheral clock as counter clock or of selected Reload timer underflow as clock input
- Can be triggered by software or reload timer
- Can trigger ADC conversion
- Timing point capture
- Start delay

Quadrature Position/Revolution Counter (QPRC)

- Up/down count mode, Phase difference count mode, Count mode with direction
- 16-bit position counter
- 16-bit revolution counter
- Two 16-bit compare registers with interrupt
- Detection edge of the three external event input pins AIN, BIN and ZIN is configurable

Real Time Clock

- Operational on main oscillation (4MHz), sub oscillation (32kHz) or RC oscillation (100kHz/2MHz)
- Capable to correct oscillation deviation of Sub clock or RC oscillator clock (clock calibration)
- Read/write accessible second/minute/hour registers
- Can signal interrupts every half second/second/minute/hour/day
- Internal clock divider and prescaler provide exact 1s clock

External Interrupts

- Edge or Level sensitive
- Interrupt mask bit per channel
- Each available CAN channel RX has an external interrupt for wake-up
- Selected USART channels SIN have an external interrupt for wake-up

Non Maskable Interrupt

- Disabled after reset, can be enabled by Boot-ROM depending on ROM configuration block
- Once enabled, can not be disabled other than by reset
- High or Low level sensitive
- Pin shared with external interrupt 0

I/O Ports

- Most of the external pins can be used as general purpose I/O
- All push-pull outputs (except when used as I²C SDA/SCL line)
- Bit-wise programmable as input/output or peripheral signal
- Bit-wise programmable input enable
- One input level per GPIO-pin (either Automotive or CMOS hysteresis)
- Bit-wise programmable pull-up resistor

Built-in On Chip Debugger (OCD)

- One-wire debug tool interface
- Break function:
 - Hardware break: 6 points (shared with code event)
 - Software break: 4096 points
- Event function
 - Code event: 6 points (shared with hardware break)
 - Data event: 6 points
 - Event sequencer: 2 levels + reset
- Execution time measurement function
- Trace function: 42 branches
- Security function

Flash Memory

- Dual operation flash allowing reading of one Flash bank while programming or erasing the other bank
- Command sequencer for automatic execution of programming algorithm and for supporting DMA for programming of the Flash Memory
- Supports automatic programming, Embedded Algorithm
- Write/Erase/Erase-Suspend/Resume commands
- A flag indicating completion of the automatic algorithm
- Erase can be performed on each sector individually
- Sector protection
- Flash Security feature to protect the content of the Flash
- Low voltage detection during Flash erase or write

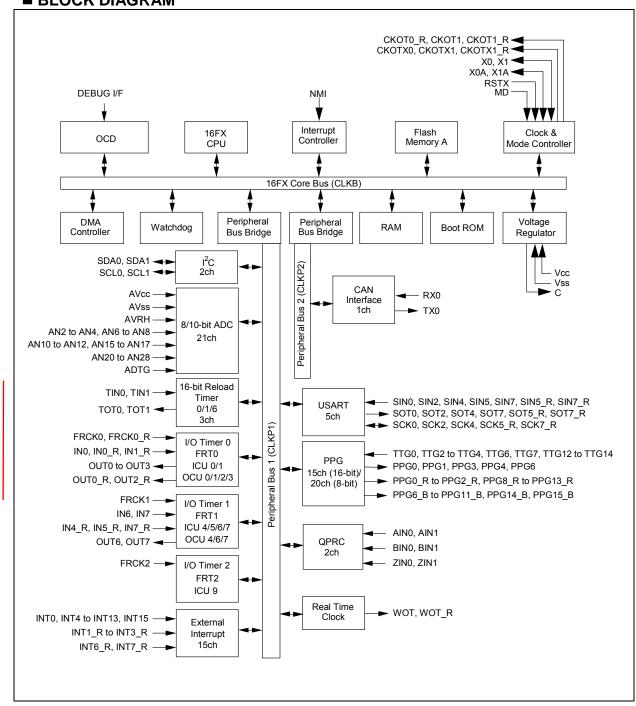
■ PRODUCT LINEUP

Features		MB96630	Remark	
Product Type		Flash Memory Product	. coman	
Subclock		Subclock can be set by software		
Dual Operation Flash Memory RAM		-		
64.5KB + 32KB 10KB		MB96F633R, MB96F633A		
128.5KB + 32KB	16KB	MB96F635R, MB96F635A	Product Options	
256.5KB + 32KB	24KB	MB96F636R	R: MCU with CAN	
384.5KB + 32KB	24KB	MB96F637R	A: MCU without CAN	
	ZOKD	LQFP-80		
Package		FPT-80P-M21		
DMA		4ch		
USART		5ch	LIN-USART 0/2/4/5/7	
with automatic LIN	-Header			
transmission/recepti		Yes (only 1ch)	LIN-USART 0	
with 16 byte RX-an				
TX-FIFO		No		
I ² C		2ch	I ² C 0/1	
			AN 2 to 4/6 to 8/	
8/10-bit A/D Converter		21ch	10 to 12/15 to 17/20 to 28	
with Data Buffer		No		
with Range Compar	rator	Yes		
with Scan Disable		Yes		
with ADC Pulse De	tection	No		
16-bit Reload Timer (RLT)	<u>teetion</u>	3ch	RLT 0/1/6	
16-bit Free-Running Timer (FRT)		3ch	FRT 0 to 2	
	10-bit Free-Kuilling Timer (FKT)		ICU 0/1/4 to 7/9	
16-bit Input Capture Unit (ICU)		7ch (1 channel for LIN-USART)	(ICU 9 for LIN-USART)	
		(1 channel for Env object)	OCU 0 to 4/6/7	
16-bit Output Compare Unit (C	OCU)	7ch	(OCU 4 for FRT clear)	
8/16-bit Programmable Pulse C	Generator	15.1 (16.1%) (20.1 (0.1%)	, ,	
(PPG)		15ch (16-bit) / 20ch (8-bit)	PPG 0 to 4/6 to 15	
with Timing point c	apture	Yes		
with Start delay		Yes		
with Ramp		No		
Quadrature Position/Revolution	n Counter		ODD C 0/1	
(QPRC)		2ch	QPRC 0/1	
		1ch	CAN 0	
CAN IIIIerrace	CAN Interface		32 Message Buffers	
External Interrupts (INT)			T3 TTT 0 4 4 4 4 5	
External Interrupts (INT)		15ch	INT 0 to 13/15	
)	15ch 1ch	INT 0 to 13/15	
External Interrupts (INT) Non-Maskable Interrupt (NMI) Real Time Clock (RTC))		INT 0 to 13/15	
Non-Maskable Interrupt (NMI) Real Time Clock (RTC))	1ch	INT 0 to 13/15	
Non-Maskable Interrupt (NMI) Real Time Clock (RTC))	1ch 1ch	INT 0 to 13/15	
Non-Maskable Interrupt (NMI) Real Time Clock (RTC) I/O Ports)	1ch 1ch 62 (Dual clock mode)	INT 0 to 13/15	
Non-Maskable Interrupt (NMI) Real Time Clock (RTC) I/O Ports)	1ch 1ch 62 (Dual clock mode) 64 (Single clock mode)	INT 0 to 13/15	
Non-Maskable Interrupt (NMI) Real Time Clock (RTC) I/O Ports Clock Calibration Unit (CAL) Clock Output Function		1ch 1ch 62 (Dual clock mode) 64 (Single clock mode) 1ch	Low voltage detection function can be	
Non-Maskable Interrupt (NMI) Real Time Clock (RTC) I/O Ports Clock Calibration Unit (CAL) Clock Output Function Low Voltage Detection Function		1ch 1ch 62 (Dual clock mode) 64 (Single clock mode) 1ch 2ch	Low voltage detection	
Non-Maskable Interrupt (NMI) Real Time Clock (RTC) I/O Ports Clock Calibration Unit (CAL)		1ch 1ch 62 (Dual clock mode) 64 (Single clock mode) 1ch 2ch Yes	Low voltage detection function can be	

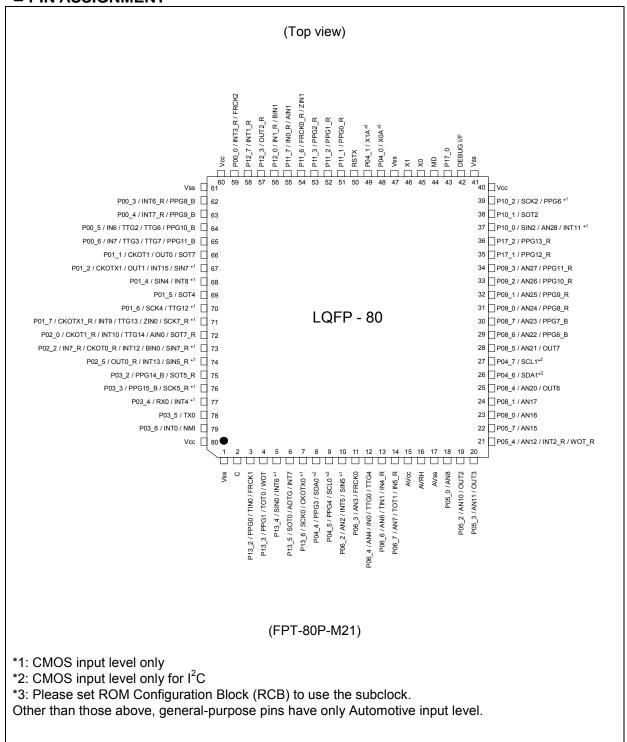
Note: All signals of the peripheral function in each product cannot be allocated by limiting the pins of package. It is necessary to use the port relocate function of the general I/O port according to your function use.

■ BLOCK DIAGRAM

6



■ PIN ASSIGNMENT



■ PIN DESCRIPTION

■ PIN DESCR		5		
Pin name	Feature	Description		
ADTG	ADC	A/D converter trigger input pin		
AINn	QPRC	Quadrature Position/Revolution Counter Unit n input pin		
ANn	ADC	A/D converter channel n input pin		
AVcc	Supply	Analog circuits power supply pin		
AVRH	ADC	A/D converter high reference voltage input pin		
AVss	Supply	Analog circuits power supply pin		
BINn	QPRC	Quadrature Position/Revolution Counter Unit n input pin		
С	Voltage regulator	Internally regulated power supply stabilization capacitor pin		
CKOTn	Clock Output function	Clock Output function n output pin		
CKOTn_R	Clock Output function	Relocated Clock Output function n output pin		
CKOTXn	Clock Output function	Clock Output function n inverted output pin		
CKOTXn_R	Clock Output function	Relocated Clock Output function n inverted output pin		
DEBUG I/F	OCD	On Chip Debugger input/output pin		
FRCKn	Free-Running Timer	Free-Running Timer n input pin		
FRCKn_R	Free-Running Timer	Relocated Free-Running Timer n input pin		
INn	ICU	Input Capture Unit n input pin		
INn_R	ICU	Relocated Input Capture Unit n input pin		
INTn	External Interrupt	External Interrupt n input pin		
INTn_R	External Interrupt	Relocated External Interrupt n input pin		
MD	Core	Input pin for specifying the operating mode		
NMI	External Interrupt	Non-Maskable Interrupt input pin		
OUTn	OCU	Output Compare Unit n waveform output pin		
OUTn_R	OCU	Relocated Output Compare Unit n waveform output pin		
Pnn_m	GPIO	General purpose I/O pin		
PPGn	PPG	Programmable Pulse Generator n output pin (16bit/8bit)		
PPGn_R	PPG	Relocated Programmable Pulse Generator n output pin (16bit/8bit)		
PPGn_B	PPG	Programmable Pulse Generator n output pin (16bit/8bit)		
RSTX	Core	Reset input pin		
RXn	CAN	CAN interface n RX input pin		
SCKn	USART	USART n serial clock input/output pin		
SCKn_R	USART	Relocated USART n serial clock input/output pin		
SCLn	I ² C	I ² C interface n clock I/O input/output pin		
SDAn	I^2C	I ² C interface n serial data I/O input/output pin		
SINn	USART	USART n serial data input pin		
SINn_R	USART	Relocated USART n serial data input pin		
SOTn	USART	USART n serial data output pin		
SOTn_R	USART	Relocated USART n serial data output pin		
TINn	Reload Timer	Reload Timer n event input pin		
TOTn	Reload Timer	Reload Timer n output pin		
TTGn	PPG	Programmable Pulse Generator n trigger input pin		
TXn	CAN	CAN interface n TX output pin		
Vcc	Supply	Power supply pin		
Vss	Supply	Power supply pin		
WOT	RTC	Real Time clock output pin		
		-		

Pin name	Feature	Description	
WOT_R	RTC	Relocated Real Time clock output pin	
X0	Clock	Oscillator input pin	
X0A	Clock	Subclock Oscillator input pin	
X1	Clock	Oscillator output pin	
X1A	Clock	Subclock Oscillator output pin	
ZINn	QPRC	Quadrature Position/Revolution Counter Unit n input pin	

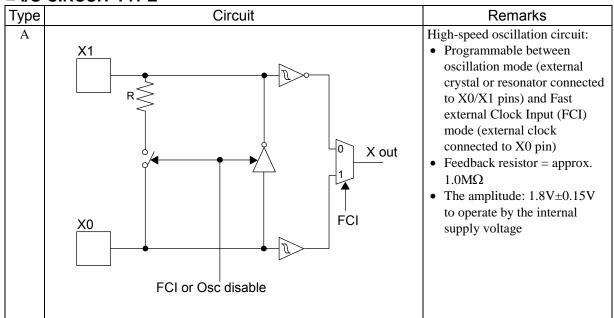
■ PIN CIRCUIT TYPE

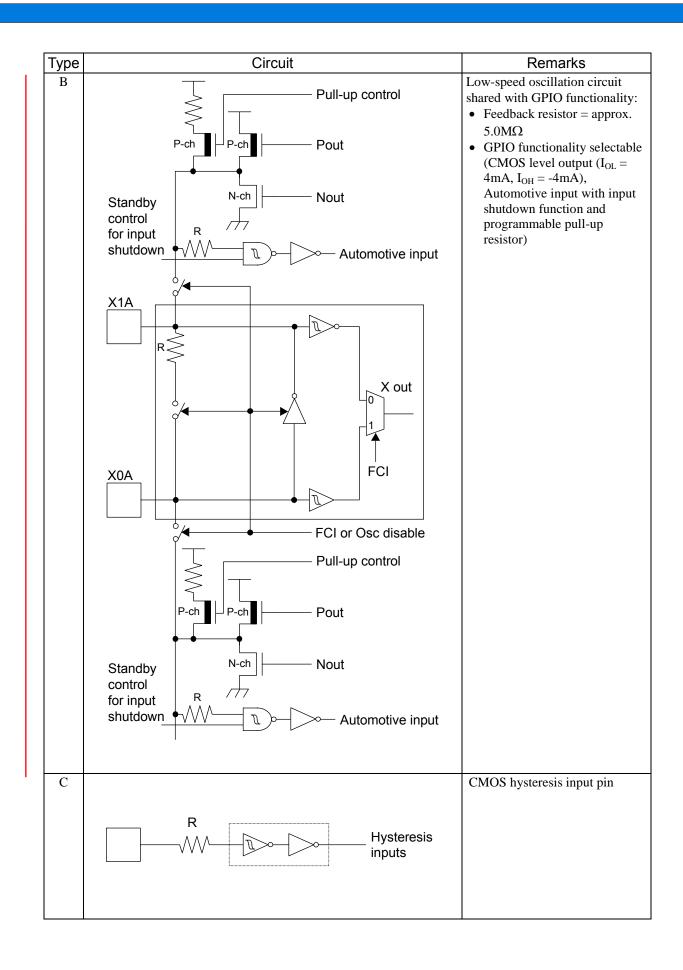
Pin no.	I/O circuit type*	Pin name
1	Supply	Vss
2	F	С
3	Н	P13_2 / PPG0 / TIN0 / FRCK1
4	Н	P13_3 / PPG1 / TOT0 / WOT
5	M	P13_4 / SIN0 / INT6
6	Н	P13_5 / SOT0 / ADTG / INT7
7	M	P13_6 / SCK0 / CKOTX0
8	N	P04_4 / PPG3 / SDA0
9	N	P04_5 / PPG4 / SCL0
10	I	P06_2 / AN2 / INT5 / SIN5
11	K	P06_3 / AN3 / FRCK0
12	K	P06_4 / AN4 / IN0 / TTG0 / TTG4
13	K	P06_6 / AN6 / TIN1 / IN4_R
14	K	P06_7 / AN7 / TOT1 / IN5_R
15	Supply	AVcc
16	G	AVRH
17	Supply	AVss
18	K	P05_0 / AN8
19	K	P05_2 / AN10 / OUT2
20	K	P05_3 / AN11 / OUT3
21	K	P05_4 / AN12 / INT2_R / WOT_R
22	K	P05_7 / AN15
23	K	P08_0 / AN16
24	K	P08_1 / AN17
25	K	P08_4 / AN20 / OUT6
26	N	P04_6 / SDA1
27	N	P04_7 / SCL1
28	K	P08_5 / AN21 / OUT7
29	K	P08_6 / AN22 / PPG6_B
30	K	P08_7 / AN23 / PPG7_B
31	K	P09_0 / AN24 / PPG8_R
32	K	P09_1 / AN25 / PPG9_R
33	K	P09_2 / AN26 / PPG10_R
34	K	P09_3 / AN27 / PPG11_R
35	Н	P17_1 / PPG12_R
36	Н	P17_2 / PPG13_R
37	I	P10_0 / SIN2 / AN28 / INT11
38	Н	P10_1 / SOT2
39	M	P10_2 / SCK2 / PPG6
40	Supply	Vcc

Pin no.	I/O circuit type*	Pin name	
41	Supply	Vss	
42	0	DEBUG I/F	
43	Н	P17_0	
44	C	MD	
45	A	X0	
46	A	X1	
47	Supply	Vss	
48	В	P04_0 / X0A	
49	В	P04_1 / X1A	
50	С	RSTX	
51	Н	P11_1 / PPG0_R	
52	Н	P11_2 / PPG1_R	
53	Н	P11_3 / PPG2_R	
54	Н	P11_6 / FRCK0_R / ZIN1	
55	Н	P11_7 / IN0_R / AIN1	
56	Н	P12_0 / IN1_R / BIN1	
57	Н	P12_3 / OUT2_R	
58	Н	P12_7 / INT1_R	
59	Н	P00_0 / INT3_R / FRCK2	
60	Supply	Vcc	
61	Supply	Vss	
62	Н	P00_3 / INT6_R / PPG8_B	
63	Н	P00_4 / INT7_R / PPG9_B	
64	Н	P00_5 / IN6 / TTG2 / TTG6 / PPG10_B	
65	Н	P00_6 / IN7 / TTG3 / TTG7 / PPG11_B	
66	Н	P01_1 / CKOT1 / OUT0 / SOT7	
67	M	P01_2 / CKOTX1 / OUT1 / INT15 / SIN7	
68	M	P01_4 / SIN4 / INT8	
69	Н	P01_5 / SOT4	
70	M	P01_6 / SCK4 / TTG12	
71	M	P01_7 / CKOTX1_R / INT9 / TTG13 / ZIN0 / SCK7_R	
72	Н	P02_0 / CKOT1_R / INT10 / TTG14 / AIN0 / SOT7_R	
73	M	P02_2 / IN7_R / CKOT0_R / INT12 / BIN0 / SIN7_R	
74	M	P02_5 / OUT0_R / INT13 / SIN5_R	
75	Н	P03_2 / PPG14_B / SOT5_R	
76	M	P03_3 / PPG15_B / SCK5_R	
77	M	P03_4 / RX0 / INT4	
78	Н	P03_5 / TX0	
79	Н	P03_6 / INT0 / NMI	
80	Supply	Vcc	

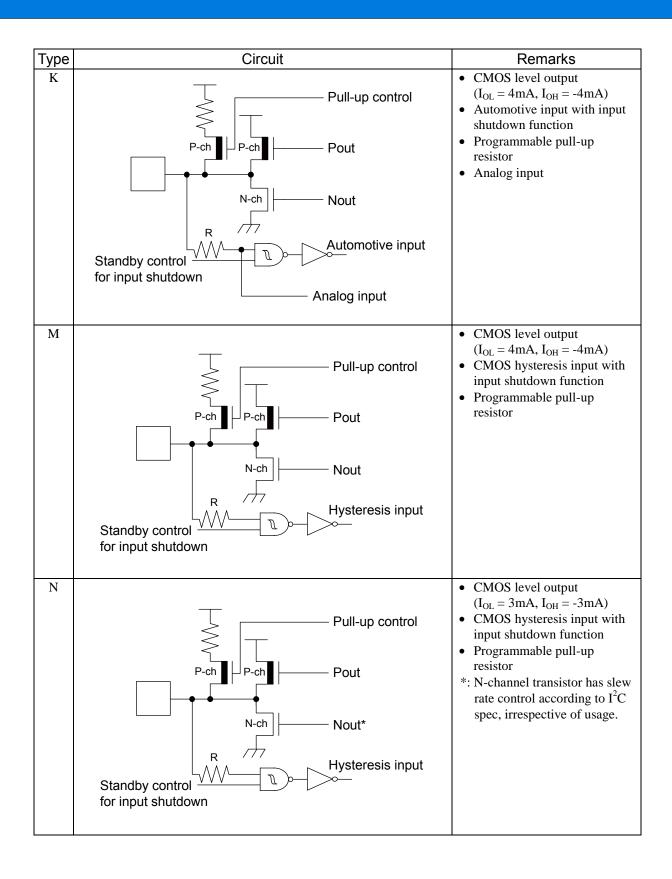
^{*:} See " \blacksquare I/O CIRCUIT TYPE" for details on the I/O circuit types.

■ I/O CIRCUIT TYPE





Туре	Circuit	Remarks
F	P-ch N-ch	Power supply input protection circuit
G	P-ch N-ch	 A/D converter ref+ (AVRH) power supply input pin with protection circuit Without protection circuit against V_{CC} for pins AVRH
Н	Pull-up control P-ch P-ch Nout Nout Automotive input for input shutdown	 CMOS level output (I_{OL} = 4mA, I_{OH} = -4mA) Automotive input with input shutdown function Programmable pull-up resistor
I	Pull-up control P-ch P-ch Pout Nout Nout Hysteresis input for input shutdown Analog input	 CMOS level output (I_{OL} = 4mA, I_{OH} = -4mA) CMOS hysteresis input with input shutdown function Programmable pull-up resistor Analog input



Type	Circuit	Remarks
O	Standby control TTL input for input shutdown	 Open-drain I/O Output 25mA, Vcc = 2.7V TTL input

■ MEMORY MAP

USER ROM*1
Reserved
Boot-ROM
Peripheral
Reserved
ROM/RAM
MIRROR
Internal RAM bank0
Reserved
Peripheral
GPR*3
DMA
Reserved
Peripheral

^{*1:} For details about USER ROM area, see "■USER ROM MEMORY MAP FOR FLASH DEVICES" on the following pages.

The DMA area is only available if the device contains the corresponding resource.

The available RAM and ROM area depends on the device.

^{*2:} For RAMSTART addresses, see the table on the next page.

^{*3:} Unused GPR banks can be used as RAM area. GPR: General-Purpose Register

■ RAMSTART ADDRESSES

Devices	Bank 0 RAM size	RAMSTART0
MB96F633	10KB	$00:5A00_{H}$
MB96F635	16KB	00:4200 _H
MB96F636	24KB	00:2200 _H
MB96F637	28KB	00:1200 _H

■ USER ROM MEMORY MAP FOR FLASH DEVICES

		MB96F633	MB96F635	MB96F636	MB96F637	
CPU mode address	Flash memory mode address	Flash size 64.5KB + 32KB	Flash size 128.5KB + 32KB	Flash size 256.5KB + 32KB	Flash size 384.5KB + 32KB	
FF:FFFF _H FF:0000 _H	3F:FFFF _H 3F:0000 _H	SA39 - 64KB	SA39 - 64KB	SA39 - 64KB	SA39 - 64KB	
FE:FFFF _H FE:0000 _H	3E:FFF _H 3E:0000 _H		SA38 - 64KB	SA38 - 64KB	SA38 - 64KB	
FD:FFFF _H FD:0000 _H	3D:FFFF _H 3D:0000 _H			SA37 - 64KB	SA37 - 64KB	Bank A of Flasi
FC:FFFF _H FC:0000 _H	3C:FFFF _H 3C:0000 _H			SA36 - 64KB	SA36 - 64KB	Dank A Oi I lasi
FB:FFFF _H FB:0000 _H	3B:FFFF _H 3B:0000 _H				SA35 - 64KB	
FA:FFFF _H FA:0000 _H F9:FFFF _H	3A:FFFF _H 3A:0000 _H				SA34 - 64KB	
DF:A000 _H		Reserved	Reserved	Reserved	Reserved	
DF:9FFF _H DF:8000 _H	1F:9FFF _H 1F:8000 _H	SA4 - 8KB	SA4 - 8KB	SA4 - 8KB	SA4 - 8KB	
DF:7FFF _H DF:6000 _H	1F:7FFF _H 1F:6000 _H	SA3 - 8KB	SA3 - 8KB	SA3 - 8KB	SA3 - 8KB	Bank B of Flash
DF:5FFF _H DF:4000 _H	1F:5FFF _H 1F:4000 _H	SA2 - 8KB	SA2 - 8KB	SA2 - 8KB	SA2 - 8KB	Dalik D OI Flasi
DF:3FFF _H	1F:3FFF _H 1F:2000 _H	SA1 - 8KB	SA1 - 8KB	SA1 - 8KB	SA1 - 8KB	
DF:2000 _H						D 1 - A 4 1
DF:2000 _H DF:1FFF _H DF:0000 _H	1F:1FFF _H 1F:0000 _H	SAS - 512B*	SAS - 512B*	SAS - 512B*	SAS - 512B*	Bank A of Flas

*: Physical address area of SAS-512B is from DF:0000 $_{\rm H}$ to DF:01FF $_{\rm H}$. Others (from DF:0200 $_{\rm H}$ to DF:1FFF $_{\rm H}$) is mirror area of SAS-512B. Sector SAS contains the ROM configuration block RCBA at CPU address DF:0000 $_{\rm H}$ -DF:01FF $_{\rm H}$. SAS can not be used for E²PROM emulation.

■ SERIAL PROGRAMMING COMMUNICATION INTERFACE

USART pins for Flash serial programming (MD = 0, DEBUG I/F = 0, Serial Communication mode)

MB96630				
Pin Number	Pin Number USART Number			
5		SIN0		
6	USART0	SOT0		
7		SCK0		
37		SIN2		
38	USART2	SOT2		
39		SCK2		
68		SIN4		
69	USART4	SOT4		
70		SCK4		

■ INTERRUPT VECTOR TABLE

Vector number	Offset in vector table	Vector name	Cleared by DMA	Index in ICR to program	Description
0	$3FC_H$	CALLV0	No	-	CALLV instruction
1	$3F8_{H}$	CALLV1	No	-	CALLV instruction
2	$3F4_{H}$	CALLV2	No	-	CALLV instruction
3	$3F0_{H}$	CALLV3	No	-	CALLV instruction
4	$3EC_H$	CALLV4	No	-	CALLV instruction
5	3E8 _H	CALLV5	No	ı	CALLV instruction
6	3E4 _H	CALLV6	No	-	CALLV instruction
7	$3E0_{H}$	CALLV7	No	-	CALLV instruction
8	3DC _H	RESET	No	-	Reset vector
9	3D8 _H	INT9	No	-	INT9 instruction
10	3D4 _H	EXCEPTION	No	-	Undefined instruction execution
11	$3D0_{H}$	NMI	No	-	Non-Maskable Interrupt
12	3CC _H	DLY	No	12	Delayed Interrupt
13	3C8 _H	RC_TIMER	No	13	RC Clock Timer
14	3C4 _H	MC_TIMER	No	14	Main Clock Timer
15	3C0 _H	SC_TIMER	No	15	Sub Clock Timer
16	3BC _H	LVDI	No	16	Low Voltage Detector
17	3B8 _H	EXTINT0	Yes	17	External Interrupt 0
18	3B4 _H	EXTINT1	Yes	18	External Interrupt 1
19	$3B0_{H}$	EXTINT2	Yes	19	External Interrupt 2
20	3AC _H	EXTINT3	Yes	20	External Interrupt 3
21	3A8 _H	EXTINT4	Yes	21	External Interrupt 4
22	$3A4_{H}$	EXTINT5	Yes	22	External Interrupt 5
23	$3A0_{H}$	EXTINT6	Yes	23	External Interrupt 6
24	39C _H	EXTINT7	Yes	24	External Interrupt 7
25	398 _H	EXTINT8	Yes	25	External Interrupt 8
26	394 _H	EXTINT9	Yes	26	External Interrupt 9
27	390 _H	EXTINT10	Yes	27	External Interrupt 10
28	38C _H	EXTINT11	Yes	28	External Interrupt 11
29	388 _H	EXTINT12	Yes	29	External Interrupt 12
30	384 _H	EXTINT13	Yes	30	External Interrupt 13
31	380 _H	-	-	31	Reserved
32	37C _H	EXTINT15	Yes	32	External Interrupt 15
33	378 _H	CAN0	No	33	CAN Controller 0
34	374 _H	-	-	34	Reserved
35	370 _H	-	-	35	Reserved
36	36C _H	-	-	36	Reserved
37	368 _H	-	-	37	Reserved
38	364 _H	PPG0	Yes	38	Programmable Pulse Generator 0
39	360 _H	PPG1	Yes	39	Programmable Pulse Generator 1
40	35C _H	PPG2	Yes	40	Programmable Pulse Generator 2

Vector number	Offset in vector table	Vector name	Cleared by DMA	Index in ICR to program	Description
41	358 _H	PPG3	Yes	41	Programmable Pulse Generator 3
42	354 _H	PPG4	Yes	42	Programmable Pulse Generator 4
43	$350_{\rm H}$	-	-	43	Reserved
44	34C _H	PPG6	Yes	44	Programmable Pulse Generator 6
45	348 _H	PPG7	Yes	45	Programmable Pulse Generator 7
46	344 _H	PPG8	Yes	46	Programmable Pulse Generator 8
47	340 _H	PPG9	Yes	47	Programmable Pulse Generator 9
48	33C _H	PPG10	Yes	48	Programmable Pulse Generator 10
49	338 _H	PPG11	Yes	49	Programmable Pulse Generator 11
50	334 _H	PPG12	Yes	50	Programmable Pulse Generator 12
51	$330_{\rm H}$	PPG13	Yes	51	Programmable Pulse Generator 13
52	32C _H	PPG14	Yes	52	Programmable Pulse Generator 14
53	328_{H}	PPG15	Yes	53	Programmable Pulse Generator 15
54	$324_{\rm H}$	-	-	54	Reserved
55	$320_{\rm H}$	-	-	55	Reserved
56	31C _H	-	-	56	Reserved
57	318 _H	-	-	57	Reserved
58	$314_{\rm H}$	RLT0	Yes	58	Reload Timer 0
59	$310_{\rm H}$	RLT1	Yes	59	Reload Timer 1
60	30C _H	-	-	60	Reserved
61	308 _H	-	-	61	Reserved
62	304 _H	-	-	62	Reserved
63	300 _H	-	-	63	Reserved
64	2FC _H	RLT6	Yes	64	Reload Timer 6
65	2F8 _H	ICU0	Yes	65	Input Capture Unit 0
66	2F4 _H	ICU1	Yes	66	Input Capture Unit 1
67	$2F0_{H}$	-	-	67	Reserved
68	2EC _H	-	-	68	Reserved
69	2E8 _H	ICU4	Yes	69	Input Capture Unit 4
70	2E4 _H	ICU5	Yes	70	Input Capture Unit 5
71	2E0 _H	ICU6	Yes	71	Input Capture Unit 6
72	2DC _H	ICU7	Yes	72	Input Capture Unit 7
73	2D8 _H	-	-	73	Reserved
74	2D4 _H	ICU9	Yes	74	Input Capture Unit 9
75	2D0 _H	-	-	75	Reserved
76	2CC _H	-	-	76	Reserved
77	2C8 _H	OCU0	Yes	77	Output Compare Unit 0
78	2C4 _H	OCU1	Yes	78	Output Compare Unit 1
79	2C0 _H	OCU2	Yes	79	Output Compare Unit 2
80	2BC _H	OCU3	Yes	80	Output Compare Unit 3

Vector number	Offset in vector table	Vector name	Cleared by DMA	Index in ICR to program	Description
81	2B8 _H	OCU4	Yes	81	Output Compare Unit 4
82	$2B4_{H}$	-	-	82	Reserved
83	$2B0_{H}$	OCU6	Yes	83	Output Compare Unit 6
84	$2AC_H$	OCU7	Yes	84	Output Compare Unit 7
85	$2A8_{H}$	-	-	85	Reserved
86	$2A4_{H}$	-	-	86	Reserved
87	$2A0_{H}$	-	-	87	Reserved
88	29C _H	-	-	88	Reserved
89	$298_{\rm H}$	FRT0	Yes	89	Free-Running Timer 0
90	$294_{\rm H}$	FRT1	Yes	90	Free-Running Timer 1
91	290_{H}	FRT2	Yes	91	Free-Running Timer 2
92	28C _H	-	-	92	Reserved
93	288 _H	RTC0	No	93	Real Time Clock
94	$284_{\rm H}$	CAL0	No	94	Clock Calibration Unit
95	$280_{\rm H}$	-	-	95	Reserved
96	27C _H	IIC0	Yes	96	I ² C interface 0
97	278 _H	IIC1	Yes	97	I ² C interface 1
98	$274_{\rm H}$	ADC0	Yes	98	A/D Converter 0
99	270_{H}	-	-	99	Reserved
100	26C _H	-	-	100	Reserved
101	268 _H	LINR0	Yes	101	LIN USART 0 RX
102	264 _H	LINT0	Yes	102	LIN USART 0 TX
103	260_{H}	-	-	103	Reserved
104	25C _H	-	-	104	Reserved
105	258 _H	LINR2	Yes	105	LIN USART 2 RX
106	254 _H	LINT2	Yes	106	LIN USART 2 TX
107	250_{H}	-	-	107	Reserved
108	24C _H	-	-	108	Reserved
109	248 _H	LINR4	Yes	109	LIN USART 4 RX
110	$244_{\rm H}$	LINT4	Yes	110	LIN USART 4 TX
111	$240_{\rm H}$	LINR5	Yes	111	LIN USART 5 RX
112	23C _H	LINT5	Yes	112	LIN USART 5 TX
113	238 _H	-	-	113	Reserved
114	234 _H	-	-	114	Reserved
115	230_{H}	LINR7	Yes	115	LIN USART 7 RX
116	$22C_{\mathrm{H}}$	LINT7	Yes	116	LIN USART 7 TX
117	228_{H}	-	-	117	Reserved
118	224 _H	-	-	118	Reserved
119	220_{H}	-	-	119	Reserved
120	21C _H	-	-	120	Reserved

Vector number	Offset in vector table	Vector name	Cleared by DMA	Index in ICR to program	Description
121	218 _H	-	-	121	Reserved
122	214 _H	-	-	122	Reserved
123	$210_{\rm H}$	-	-	123	Reserved
124	20C _H	-	-	124	Reserved
125	208 _H	-	-	125	Reserved
126	204 _H	-	-	126	Reserved
127	$200_{\rm H}$	-	-	127	Reserved
128	1FC _H	-	-	128	Reserved
129	1F8 _H	-	-	129	Reserved
130	1F4 _H	-	-	130	Reserved
131	1F0 _H	-	-	131	Reserved
132	1EC _H	-	-	132	Reserved
133	1E8 _H	FLASHA	Yes	133	Flash memory A interrupt
134	1E4 _H	-	-	134	Reserved
135	1E0 _H	-	-	135	Reserved
136	1DC _H	-	-	136	Reserved
137	1D8 _H	QPRC0	Yes	137	Quadrature Position/Revolution counter 0
138	1D4 _H	QPRC1	Yes	138	Quadrature Position/Revolution counter 1
139	$1D0_{H}$	ADCRC0	No	139	A/D Converter 0 - Range Comparator
140	1CC _H	-	-	140	Reserved
141	1C8 _H	-	-	141	Reserved
142	1C4 _H	-	-	142	Reserved
143	1C0 _H	-	-	143	Reserved

Code: DS00-00004-1Ea

■ HANDLING PRECAUTIONS

Any semiconductor devices have inherently a certain rate of failure. The possibility of failure is greatly affected by the conditions in which they are used (circuit conditions, environmental conditions, etc.). This page describes precautions that must be observed to minimize the chance of failure and to obtain higher reliability from your FUJITSU SEMICONDUCTOR semiconductor devices.

1. Precautions for Product Design

This section describes precautions when designing electronic equipment using semiconductor devices.

Absolute Maximum Ratings

Semiconductor devices can be permanently damaged by application of stress (voltage, current, temperature, etc.) in excess of certain established limits, called absolute maximum ratings. Do not exceed these ratings.

Recommended Operating Conditions

Recommended operating conditions are normal operating ranges for the semiconductor device. All the device's electrical characteristics are warranted when operated within these ranges.

Always use semiconductor devices within the recommended operating conditions. Operation outside these ranges may adversely affect reliability and could result in device failure.

No warranty is made with respect to uses, operating conditions, or combinations not represented on the data sheet. Users considering application outside the listed conditions are advised to contact their sales representative beforehand.

· Processing and Protection of Pins

These precautions must be followed when handling the pins which connect semiconductor devices to power supply and input/output functions.

(1) Preventing Over-Voltage and Over-Current Conditions

Exposure to voltage or current levels in excess of maximum ratings at any pin is likely to cause deterioration within the device, and in extreme cases leads to permanent damage of the device. Try to prevent such overvoltage or over-current conditions at the design stage.

(2) Protection of Output Pins

Shorting of output pins to supply pins or other output pins, or connection to large capacitance can cause large current flows. Such conditions if present for extended periods of time can damage the device.

Therefore, avoid this type of connection.

(3) Handling of Unused Input Pins

Unconnected input pins with very high impedance levels can adversely affect stability of operation. Such pins should be connected through an appropriate resistance to a power supply pin or ground pin.

· Latch-up

Semiconductor devices are constructed by the formation of P-type and N-type areas on a substrate. When subjected to abnormally high voltages, internal parasitic PNPN junctions (called thyristor structures) may be formed, causing large current levels in excess of several hundred mA to flow continuously at the power supply pin. This condition is called latch-up.

CAUTION: The occurrence of latch-up not only causes loss of reliability in the semiconductor device, but can cause injury or damage from high heat, smoke or flame. To prevent this from happening, do the following:

- (1) Be sure that voltages applied to pins do not exceed the absolute maximum ratings. This should include attention to abnormal noise, surge levels, etc.
- (2) Be sure that abnormal current flows do not occur during the power-on sequence.

Observance of Safety Regulations and Standards

Most countries in the world have established standards and regulations regarding safety, protection from electromagnetic interference, etc. Customers are requested to observe applicable regulations and standards in the design of products.

· Fail-Safe Design

Any semiconductor devices have inherently a certain rate of failure. You must protect against injury, damage or loss from such failures by incorporating safety design measures into your facility and equipment such as redundancy, fire protection, and prevention of over-current levels and other abnormal operating conditions.

Precautions Related to Usage of Devices

FUJITSU SEMICONDUCTOR semiconductor devices are intended for use in standard applications (computers, office automation and other office equipment, industrial, communications, and measurement equipment, personal or household devices, etc.).

CAUTION: Customers considering the use of our products in special applications where failure or abnormal operation may directly affect human lives or cause physical injury or property damage, or where extremely high levels of reliability are demanded (such as aerospace systems, atomic energy controls, sea floor repeaters, vehicle operating controls, medical devices for life support, etc.) are requested to consult with sales representatives before such use. The company will not be responsible for damages arising from such use without prior approval.

2. Precautions for Package Mounting

Package mounting may be either lead insertion type or surface mount type. In either case, for heat resistance during soldering, you should only mount under FUJITSU SEMICONDUCTOR's recommended conditions. For detailed information about mount conditions, contact your sales representative.

· Lead Insertion Type

Mounting of lead insertion type packages onto printed circuit boards may be done by two methods: direct soldering on the board, or mounting by using a socket.

Direct mounting onto boards normally involves processes for inserting leads into through-holes on the board and using the flow soldering (wave soldering) method of applying liquid solder. In this case, the soldering process usually causes leads to be subjected to thermal stress in excess of the absolute ratings for storage temperature. Mounting processes should conform to FUJITSU SEMICONDUCTOR recommended mounting conditions.

If socket mounting is used, differences in surface treatment of the socket contacts and IC lead surfaces can lead to contact deterioration after long periods. For this reason it is recommended that the surface treatment of socket contacts and IC leads be verified before mounting.

Surface Mount Type

Surface mount packaging has longer and thinner leads than lead-insertion packaging, and therefore leads are more easily deformed or bent. The use of packages with higher pin counts and narrower pin pitch results in increased susceptibility to open connections caused by deformed pins, or shorting due to solder bridges.

You must use appropriate mounting techniques. FUJITSU SEMICONDUCTOR recommends the solder reflow method, and has established a ranking of mounting conditions for each product. Users are advised to mount packages in accordance with FUJITSU SEMICONDUCTOR ranking of recommended conditions.

Lead-Free Packaging

CAUTION: When ball grid array (BGA) packages with Sn-Ag-Cu balls are mounted using Sn-Pb eutectic soldering, junction strength may be reduced under some conditions of use.

· Storage of Semiconductor Devices

Because plastic chip packages are formed from plastic resins, exposure to natural environmental conditions will cause absorption of moisture. During mounting, the application of heat to a package that has absorbed moisture can cause surfaces to peel, reducing moisture resistance and causing packages to crack. To prevent, do the following:

- (1) Avoid exposure to rapid temperature changes, which cause moisture to condense inside the product. Store products in locations where temperature changes are slight.
- (2) Use dry boxes for product storage. Products should be stored below 70% relative humidity, and at temperatures between 5°C and 30°C.

 When you open Dry Package that recommends humidity 40% to 70% relative humidity.
- (3) When necessary, FUJITSU SEMICONDUCTOR packages semiconductor devices in highly moisture-resistant aluminum laminate bags, with a silica gel desiccant. Devices should be sealed in their aluminum laminate bags for storage.
- (4) Avoid storing packages where they are exposed to corrosive gases or high levels of dust.

Baking

Packages that have absorbed moisture may be de-moisturized by baking (heat drying). Follow the FUJITSU SEMICONDUCTOR recommended conditions for baking.

Condition: 125°C/24 h

Static Electricity

Because semiconductor devices are particularly susceptible to damage by static electricity, you must take the following precautions:

- (1) Maintain relative humidity in the working environment between 40% and 70%. Use of an apparatus for ion generation may be needed to remove electricity.
- (2) Electrically ground all conveyors, solder vessels, soldering irons and peripheral equipment.
- (3) Eliminate static body electricity by the use of rings or bracelets connected to ground through high resistance (on the level of 1 $M\Omega$). Wearing of conductive clothing and shoes, use of conductive floor mats and other measures to minimize shock loads is recommended.
- (4) Ground all fixtures and instruments, or protect with anti-static measures.
- (5) Avoid the use of styrofoam or other highly static-prone materials for storage of completed board assemblies.

3. Precautions for Use Environment

Reliability of semiconductor devices depends on ambient temperature and other conditions as described above.

For reliable performance, do the following:

(1) Humidity

Prolonged use in high humidity can lead to leakage in devices as well as printed circuit boards. If high humidity levels are anticipated, consider anti-humidity processing.

(2) Discharge of Static Electricity

When high-voltage charges exist close to semiconductor devices, discharges can cause abnormal operation. In such cases, use anti-static measures or processing to prevent discharges.

(3) Corrosive Gases, Dust, or Oil

Exposure to corrosive gases or contact with dust or oil may lead to chemical reactions that will adversely affect the device. If you use devices in such conditions, consider ways to prevent such exposure or to protect the devices.

(4) Radiation, Including Cosmic Radiation

Most devices are not designed for environments involving exposure to radiation or cosmic radiation. Users should provide shielding as appropriate.

(5) Smoke, Flame

28

CAUTION: Plastic molded devices are flammable, and therefore should not be used near combustible substances. If devices begin to smoke or burn, there is danger of the release of toxic gases. Customers considering the use of FUJITSU SEMICONDUCTOR products in other special environmental conditions should consult with sales representatives.

Please check the latest handling precautions at the following URL. http://edevice.fujitsu.com/fj/handling-e.pdf

HANDLING DEVICES

Special care is required for the following when handling the device:

- Latch-up prevention
- Unused pins handling
- External clock usage
- Notes on PLL clock mode operation
- Power supply pins (Vcc/Vss)
- Crystal oscillator and ceramic resonator circuit
- Turn on sequence of power supply to A/D converter and analog inputs
- Pin handling when not using the A/D converter
- Notes on Power-on
- Stabilization of power supply voltage
- Serial communication
- Mode Pin (MD)

1. Latch-up prevention

CMOS IC chips may suffer latch-up under the following conditions:

- A voltage higher than V_{CC} or lower than V_{SS} is applied to an input or output pin.
- A voltage higher than the rated voltage is applied between Vcc pins and Vss pins.
- The AV_{CC} power supply is applied before the V_{CC} voltage.

Latch-up may increase the power supply current dramatically, causing thermal damages to the device. For the same reason, extra care is required to not let the analog power-supply voltage (AV_{CC} , AVRH) exceed the digital power-supply voltage.

2. Unused pins handling

Unused input pins can be left open when the input is disabled (corresponding bit of Port Input Enable register PIER = 0).

Leaving unused input pins open when the input is enabled may result in misbehavior and possible permanent damage of the device. To prevent latch-up, they must therefore be pulled up or pulled down through resistors which should be more than $2k\Omega$.

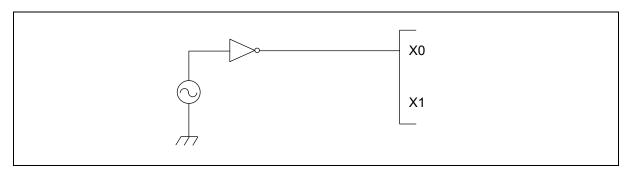
Unused bidirectional pins can be set either to the output state and be then left open, or to the input state with either input disabled or external pull-up/pull-down resistor as described above.

3. External clock usage

The permitted frequency range of an external clock depends on the oscillator type and configuration. See AC Characteristics for detailed modes and frequency limits. Single and opposite phase external clocks must be connected as follows:

(1) Single phase external clock for Main oscillator

When using a single phase external clock for the Main oscillator, X0 pin must be driven and X1 pin left open. And supply 1.8V power to the external clock.

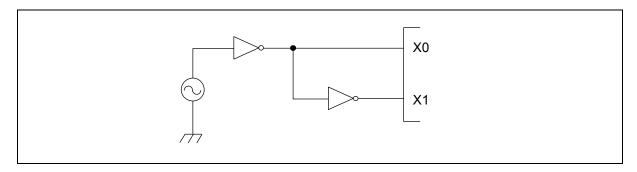


(2) Single phase external clock for Sub oscillator

When using a single phase external clock for the Sub oscillator, "External clock mode" must be selected and X0A/P04_0 pin must be driven. X1A/P04_1 pin can be configured as GPIO.

(3) Opposite phase external clock

When using an opposite phase external clock, X1 (X1A) pins must be supplied with a clock signal which has the opposite phase to the X0 (X0A) pins. Supply level on X0 and X1 pins must be 1.8V.



4. Notes on PLL clock mode operation

If the microcontroller is operated with PLL clock mode and no external oscillator is operating or no external clock is supplied, the

microcontroller attempts to work with the free oscillating PLL. Performance of this operation, however, cannot be guaranteed.

5. Power supply pins (Vcc/Vss)

It is required that all V_{CC} -level as well as all V_{SS} -level power supply pins are at the same potential. If there is more than one V_{CC} or V_{SS} level, the device may operate incorrectly or be damaged even within the guaranteed operating range.

Vcc and Vss pins must be connected to the device from the power supply with lowest possible impedance. The smoothing capacitor at Vcc pin must use the one of a capacity value that is larger than Cs.

Besides this, as a measure against power supply noise, it is required to connect a bypass capacitor of about $0.1\mu F$ between Vcc and Vss pins as close as possible to Vcc and Vss pins.

6. Crystal oscillator and ceramic resonator circuit

Noise at X0, X1 pins or X0A, X1A pins might cause abnormal operation. It is required to provide bypass capacitors with shortest possible distance to X0, X1 pins and X0A, X1A pins, crystal oscillator (or ceramic resonator) and ground lines, and, to the utmost effort, that the lines of oscillation circuit do not cross the lines of other circuits.

It is highly recommended to provide a printed circuit board art work surrounding X0, X1 pins and X0A, X1A pins with a ground area for stabilizing the operation.

It is highly recommended to evaluate the quartz/MCU or resonator/MCU system at the quartz or resonator manufacturer, especially when using low-Q resonators at higher frequencies.

7. Turn on sequence of power supply to A/D converter and analog inputs

It is required to turn the A/D converter power supply (AV $_{CC}$, AVRH) and analog inputs (ANn) on after turning the digital power supply (V $_{CC}$) on.

It is also required to turn the digital power off after turning the A/D converter supply and analog inputs off. In this case, AVRH must not exceed AV_{CC} . Input voltage for ports shared with analog input ports also must not exceed AV_{CC} (turning the analog and digital power supplies simultaneously on or off is acceptable).

8. Pin handling when not using the A/D converter

If the A/D converter is not used, the power supply pins for A/D converter should be connected such as $AV_{CC} = V_{CC}$, $AV_{SS} = AVRH = V_{SS}$.

9. Notes on Power-on

To prevent malfunction of the internal voltage regulator, supply voltage profile while turning the power supply on should be slower than $50\mu s$ from 0.2V to 2.7V.

10. Stabilization of power supply voltage

If the power supply voltage varies acutely even within the operation safety range of the V_{CC} power supply voltage, a malfunction may occur. The V_{CC} power supply voltage must therefore be stabilized. As stabilization guidelines, the power supply voltage must be stabilized in such a way that V_{CC} ripple fluctuations (peak to peak value) in the commercial frequencies (50Hz to 60Hz) fall within 10% of the standard V_{CC} power supply voltage and the transient fluctuation rate becomes $0.1V/\mu s$ or less in instantaneous fluctuation for power supply switching.

11. Serial communication

There is a possibility to receive wrong data due to noise or other causes on the serial communication. Therefore, design a printed circuit board so as to avoid noise.

Consider receiving of wrong data when designing the system. For example apply a checksum and retransmit the data if an error occurs.

12. Mode Pin (MD)

Connect the mode pin directly to Vcc or Vss pin. To prevent the device unintentionally entering test mode due to noise, lay out the printed circuit board so as to minimize the distance from the mode pin to Vcc or Vss pin and provide a low-impedance connection.

■ ELECTRICAL CHARACTERISTICS

1. Absolute Maximum Ratings

Parameter	Symbol	Condition	Rating		Unit	Remarks	
	- J		Min	Max			
Power supply voltage*1	V_{CC}	-	V _{SS} - 0.3	$V_{SS} + 6.0$	V		
Analog power supply voltage*1	AV_{CC}	-	V _{SS} - 0.3	$V_{SS} + 6.0$	V	$V_{CC} = AV_{CC}^{*2}$	
Analog reference voltage*1	AVRH	-	V _{SS} - 0.3	$V_{SS} + 6.0$	V	$AV_{CC} \ge AVRH$, $AVRH \ge AV_{SS}$	
Input voltage*1	$V_{\rm I}$	-	V _{SS} - 0.3	$V_{SS} + 6.0$	V	$V_{I} \leq V_{CC} + 0.3V^{*3}$	
Output voltage*1	$V_{\rm O}$	-	V _{SS} - 0.3	$V_{SS} + 6.0$	V	$V_0 \le V_{CC} + 0.3V^{*3}$	
Maximum Clamp Current	I_{CLAMP}	-	-4.0	+4.0	mA	Applicable to general purpose I/O pins *4	
Total Maximum Clamp Current	$\Sigma I_{CLAMP} $	-	-	21	mA	Applicable to general purpose I/O pins * ⁴	
"L" level maximum output current	I_{OL}	-	-	15	mA		
"L" level average output current	I_{OLAV}	1	-	4	mA		
"L" level maximum overall output current	ΣI_{OL}	-	-	52	mA		
"L" level average overall output current	ΣI_{OLAV}	-	-	26	mA		
"H" level maximum output current	I_{OH}	-	-	-15	mA		
"H" level average output current	I_{OHAV}	1	-	-4	mA		
"H" level maximum overall output current	ΣI_{OH}	-	-	-52	mA		
"H" level average overall output current	$\Sigma I_{ m OHAV}$	-	-	-26	mA		
Power consumption* ⁵	P_D	$T_A = +125^{\circ}C$	-	396 ^{*6}	mW		
Operating ambient temperature	T_{A}	-	-40	+125*7	°C		
Storage temperature	T _{STG}	-	-55	+150	°C		

^{*1:} This parameter is based on $V_{SS} = AV_{SS} = 0V$.

- Use within recommended operating conditions.
- Use at DC voltage (current).
- The +B signal should always be applied a limiting resistance placed between the +B signal and the microcontroller.
- The value of the limiting resistance should be set so that when the +B signal is applied the input current to the microcontroller pin does not exceed rated values, either instantaneously or for prolonged periods.

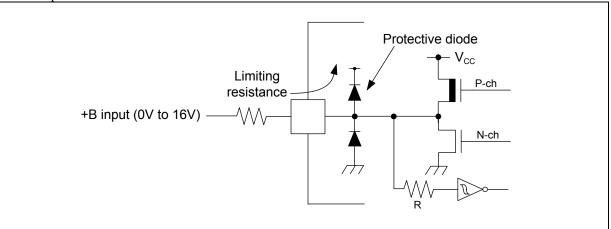
^{*2:} AV_{CC} and V_{CC} must be set to the same voltage. It is required that AV_{CC} does not exceed V_{CC} and that the voltage at the analog inputs does not exceed AV_{CC} when the power is switched on.

^{*3:} V_I and V_O should not exceed V_{CC} + 0.3V. V_I should also not exceed the specified ratings. However if the maximum current to/from an input is limited by some means with external components, the I_{CLAMP} rating supersedes the V_I rating. Input/Output voltages of standard ports depend on V_{CC} .

^{*4: •} Applicable to all general purpose I/O pins (Pnn_m).

- Note that when the microcontroller drive current is low, such as in the power saving modes, the +B input potential may pass through the protective diode and increase the potential at the V_{CC} pin, and this may affect other devices.
- Note that if a +B signal is input when the microcontroller power supply is off (not fixed at 0V), the power supply is provided from the pins, so that incomplete operation may result.
- Note that if the +B input is applied during power-on, the power supply is provided from the pins and the resulting supply voltage may not be sufficient to operate the Power reset.
- The DEBUG I/F pin has only a protective diode against V_{SS}. Hence it is only permitted to input a negative clamping current (4mA). For protection against positive input voltages, use an external clamping diode which limits the input voltage to maximum 6.0V.

• Sample recommended circuits:



*5: The maximum permitted power dissipation depends on the ambient temperature, the air flow velocity and the thermal conductance of the package on the PCB.

The actual power dissipation depends on the customer application and can be calculated as follows:

$$P_D = P_{IO} + P_{INT}$$

 $P_{IO} = \Sigma \left(V_{OL} \times I_{OL} + V_{OH} \times I_{OH} \right) \left(I/O \ load \ power \ dissipation, \ sum \ is \ performed \ on \ all \ I/O \ ports \right)$

 $P_{INT} = V_{CC} \times (I_{CC} + I_A)$ (internal power dissipation)

 I_{CC} is the total core current consumption into V_{CC} as described in the "DC characteristics" and depends on the selected operation mode and clock frequency and the usage of functions like Flash programming.

 I_{A} is the analog current consumption into $AV_{\text{CC}}.$

*6: Worst case value for a package mounted on single layer PCB at specified T_A without air flow.

*7: Write/erase to a large sector in flash memory is warranted with $T_A \le +105$ °C.

<WARNING>

Semiconductor devices can be permanently damaged by application of stress (voltage, current, temperature, etc.) in excess of absolute maximum ratings. Do not exceed these ratings.

2. Recommended Operating Conditions

 $(V_{SS} = AV_{SS} = 0V)$

Parameter	Symbol	Value			Unit	Remarks		
Farameter	Symbol	Min	Тур	Max	Offic	Remarks		
Power supply	V_{CC} , AV_{CC}	2.7	-	5.5	V			
voltage		2.0	-	5.5	V	Maintains RAM data in stop mode		
Smoothing capacitor at C pin	C_{S}	0.5	1.0 to 3.9	4.7	μF	$1.0\mu F$ (Allowance within \pm 50%) $3.9\mu F$ (Allowance within \pm 20%) Please use the ceramic capacitor or the capacitor of the frequency response of this level. The smoothing capacitor at V_{CC} must use the one of a capacity value that is larger than C_S .		

<WARNING>

The recommended operating conditions are required in order to ensure the normal operation of the semiconductor device. All of the device's electrical characteristics are warranted when the device is operated within these ranges.

Always use semiconductor devices within their recommended operating condition ranges. Operation outside these ranges may adversely affect reliability and could result in device failure. No warranty is made with respect to uses, operating conditions, or combinations not represented on the data sheet. Users considering application outside the listed conditions are advised to contact their representatives beforehand.

3. DC Characteristics

(1) Current Rating

 $(V_{CC} = AV_{CC} = 2.7V \text{ to } 5.5V, V_{SS} = AV_{SS} = 0V, T_A = -40^{\circ}C \text{ to } + 125^{\circ}C)$

Parameter	Symbol	Pin	Conditions		Value		Unit	Remarks			
Parameter	Symbol	name		Min	Тур	Max					
	I _{CCPLL}		PLL Run mode with CLKS1/2 = CLKB = CLKP1/2 = 32MHz	-	27	-	mA	$T_A = +25^{\circ}C$			
			Flash 0 wait	-	-	37	mA	$T_A = +105$ °C			
			(CLKRC and CLKSC stopped)	-	-	38.5	mA	$T_A = +125$ °C			
	I _{CCMAIN}	I _{CCRCH} Vcc I _{CCRCL}	Main Run mode with CLKS1/2 = CLKB = CLKP1/2 = 4MHz	-	3.5	-	mA	$T_A = +25$ °C			
			Flash 0 wait	-	-	8	mA	$T_A = +105$ °C			
			(CLKPLL, CLKSC and CLKRC stopped)	-	-	9.5	mA	$T_A = +125$ °C			
	I _{CCRCL}		RC Run mode with CLKS1/2 = CLKB = CLKP1/2 = CLKRC = 2MHz Flash 0 wait	-	1.8	-	mA	$T_A = +25$ °C			
Power supply current in Run				-	-	6	mA	$T_A = +105$ °C			
modes*1			(CLKMC, CLKPLL and CLKSC stopped)	-	-	7.5	mA	$T_{A} = +125^{\circ}C$			
			RC Run mode with CLKS1/2 = CLKB = CLKP1/2 = CLKRC =	-	0.16	-	mA	$T_A = +25$ °C			
						100kHz Flash 0 wait	-	-	3.5	mA	$T_A = +105$ °C
			(CLKMC, CLKPLL and CLKSC stopped)	-	-	5	mA	$T_A = +125$ °C			
			Sub Run mode with CLKS1/2 = CLKB = CLKP1/2 = 32kHz	-	0.1	-	mA	$T_A = +25$ °C			
			Flash 0 wait	-	-	3.3	mA	$T_A = +105$ °C			
			(CLKMC, CLKPLL and CLKRC stopped)	-	-	4.8	mA	$T_A = +125$ °C			

Doromotor	Cumbal	Pin	Conditions		Value		Lloit	Domarka
Parameter	Symbol	name	Conditions	Min	Тур	Max	Unit	Remarks
			PLL Sleep mode with CLKS1/2 = CLKP1/2 =	-	8.5	-	mA	$T_A = +25^{\circ}C$
	I_{CCSPLL}		32MHz (CLKRC and CLKSC	-	-	14	mA	$T_A = +105^{\circ}C$
			stopped)	-	-	15.5	mA	$T_A = +125^{\circ}C$
			Main Sleep mode with CLKS1/2 = CLKP1/2 =	-	1	-	mA	$T_A = +25^{\circ}C$
	$I_{\rm CCSMAIN}$		4MHz, $SMCR:LPMSS = 0$	-	-	4.5	mA	$T_A = +105^{\circ}C$
			(CLKPLL, CLKRC and CLKSC stopped)	-	-	6	mA	$T_A = +125^{\circ}C$
Down cumulu			Vcc RC Sleep mode with CLKS1/2 = CLKP1/2 = CLKRC = 2MHz, SMCR:LPMSS = 0	-	0.6	-	mA	$T_A = +25^{\circ}C$
Power supply current in Sleep modes*1	I_{CCSRCH}	Vcc		-	-	3.8	mA	$T_A = +105^{\circ}C$
Steep modes			(CLKMC, CLKPLL and CLKSC stopped)	-	-	5.3	mA	$T_A = +125^{\circ}C$
			RC Sleep mode with CLKS1/2 = CLKP1/2 =	-	0.07	-	mA	$T_A = +25^{\circ}C$
	I_{CCSRCL}		CLKS1/2 = CLKP1/2 = CLKRC = 100kHz (CLKMC, CLKPLL	-	-	2.8	mA	$T_A = +105^{\circ}C$
		and CLKSC stopped)	-	-	4.3	mA	$T_A = +125^{\circ}C$	
		Sub Sleep mode with	-	0.04	-	mA	$T_A = +25^{\circ}C$	
	I _{CCSSUB}		CLKS1/2 = CLKP1/2 = 32kHz, (CLKMC, CLKPLL	-	-	2.5	mA	$T_A = +105^{\circ}C$
			and CLKRC stopped)	-	-	4	mA	$T_A = +125^{\circ}C$

Parameter	Symbol	Pin	Conditions		Value		Unit	Remarks
1 arameter	Symbol	name	Conditions	Min	Тур	Max	Offic	Remarks
			PLL Timer mode with		1800	2250	μΑ	$T_A = +25^{\circ}C$
	I_{CCTPLL}		CLKPLL = 32MHz (CLKRC and CLKSC stopped)	-	-	3220	μΑ	$T_A = +105^{\circ}C$
				-	-	4205	μΑ	$T_A = +125^{\circ}C$
			Main Timer mode with	-	285	330	μΑ	$T_A = +25^{\circ}C$
	I _{CCTMAIN}		CLKMC = 4MHz, SMCR:LPMSS = 0 (CLKPLL, CLKRC and CLKSC stopped)	-	-	1195	μΑ	$T_A = +105^{\circ}C$
				-	-	2165	μΑ	$T_A = +125$ °C
Power			RC Timer mode with	-	160	215	μΑ	$T_A = +25$ °C
supply current in Timer	I _{CCTRCH}	Vcc	CLKRC = 2MHz, SMCR:LPMSS = 0 (CLKPLL, CLKMC and	-	-	1095	μΑ	$T_{A} = +105^{\circ}C$
modes*2			CLKSC stopped)	-	-	2075	μΑ	$T_A = +125^{\circ}C$
			RC Timer mode with	-	35	75	μΑ	$T_A = +25$ °C
	I_{CCTRCL}		CLKRC = 100kHz (CLKPLL, CLKMC and	-	-	905	μΑ	$T_{A} = +105^{\circ}C$
			CLKSC stopped)	-	-	1880	μΑ	$T_A = +125^{\circ}C$
			Sub Timer mode with CLKSC = 32kHz (CLKMC, CLKPLL and	-	25	65	μΑ	$T_A = +25$ °C
	I_{CCTSUB}			-	-	885	μΑ	$T_A = +105^{\circ}C$
			CLKRC stopped)	-	-	1850	μΑ	$T_{A} = +125^{\circ}C$

Parameter	Symbol	Pin	Conditions		Value		Unit	Remarks
Parameter	Syllibol	name	Conditions	Min	Тур	Max	Oill	Remarks
D				-	20	60	μΑ	$T_A = +25$ °C
Power supply current in Stop mode*3	I_{CCH}		-	-	-	880	μΑ	$T_A = +105^{\circ}C$
mode				-	ı	1845	μΑ	$T_A = +125^{\circ}C$
Flash Power Down current	I _{CCFLASHPD}		-	-	36	70	μΑ	
Power supply current		Vcc	Low voltage	-	5	-	μΑ	$T_A = +25$ °C
for active Low Voltage detector* ⁴	I_{CCLVD}		detector enabled	-	-	12.5	μΑ	$T_A = +125^{\circ}C$
Flash Write/	T			-	12.5	-	mA	$T_A = +25$ °C
Erase current*5	I _{CCFLASH}		-	-	ı	20	mA	$T_A = +125^{\circ}C$

^{*1:} The power supply current is measured with a 4MHz external clock connected to the Main oscillator and a 32kHz external clock connected to the Sub oscillator. See chapter "Standby mode and voltage regulator control circuit" of the Hardware Manual for further details about voltage regulator control. Current for "On Chip Debugger" part is not included. Power supply current in Run mode does not include Flash Write / Erase current.

^{*2}: The power supply current in Timer mode is the value when Flash is in Power-down / reset mode. When Flash is not in Power-down / reset mode, $I_{CCFLASHPD}$ must be added to the Power supply current. The power supply current is measured with a 4MHz external clock connected to the Main oscillator and a 32kHz external clock connected to the Sub oscillator. The current for "On Chip Debugger" part is not included.

^{*3:} The power supply current in Stop mode is the value when Flash is in Power-down / reset mode. When Flash is not in Power-down / reset mode, $I_{CCFLASHPD}$ must be added to the Power supply current.

^{*4:} When low voltage detector is enabled, I_{CCLVD} must be added to Power supply current.

^{*5}: When Flash Write / Erase program is executed, $I_{CCFLASH}$ must be added to Power supply current.

(2) Pin Characteristics

 $(V_{CC}=AV_{CC}=2.7V$ to 5.5V, $V_{SS}=AV_{SS}=0V,\,T_A=$ - $40^{\circ}C$ to + $125^{\circ}C)$

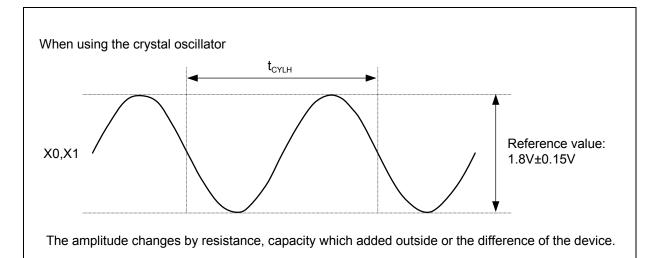
		Pin			Value	- 35 0		= - 40°C to + 125°C)
Parameter	Symbol	name	Conditions	Min	Тур	Max	Unit	Remarks
		Hame		V _{CC}	тур	V _{CC}		CMOS Hysteresis
		Port inputs	-	× 0.7	-	+ 0.3	V	input
	V_{IH}	Pnn_m		V _{CC}		V _{CC}		AUTOMOTIVE
			-	× 0.8	-	+ 0.3	V	Hysteresis input
	**	***	External clock in	VD			**	-
UYYU 1 1	V_{IHX0S}	X0	"Fast Clock Input mode"	× 0.8	-	VD	V	VD=1.8V±0.15V
"H" level	3.7	N/O A	External clock in	V_{CC}		V_{CC}	* 7	
input	V_{IHX0AS}	X0A	"Oscillation mode"	× 0.8	-	+0.3	V	
voltage	V	RSTX		V_{CC}		V _{CC}	V	CMOS Hysteresis
	V_{IHR}	KSIA	-	$\times 0.8$	-	+ 0.3	V	input
	V_{IHM}	MD		V_{CC}		V_{CC}	V	CMOS Hysteresis
	V IHM	MID	<u>-</u>	- 0.3	_	+ 0.3	v	input
	V_{IHD}	DEBUG	_	2.0	_	V_{CC}	V	TTL Input
	▼ IHD	I/F			_	+ 0.3		-
		Port	_	V_{SS}	_	V_{CC}	V	CMOS Hysteresis
	V_{IL}	inputs		- 0.3		× 0.3		input
	, IL	Pnn_m	_	V_{SS}	_	V_{CC}	V	AUTOMOTIVE
		_		- 0.3		× 0.5		Hysteresis input
	$V_{\rm ILX0S}$	X0	External clock in "Fast	V_{SS}	_	VD	V	VD=1.8V±0.15V
"L" level	ILAOS		Clock Input mode"			× 0.2		
input	$V_{\rm ILX0AS}$	X0A	External clock in	V_{SS}	-	V_{CC}	V	
voltage			"Oscillation mode"	- 0.3		× 0.2		CD LOCATE
	V_{ILR}	RSTX	-	V _{SS}	-	V_{CC}	V	CMOS Hysteresis
				- 0.3		× 0.2		input
	$V_{\rm ILM}$	MD	-	V _{SS} - 0.3	-	$V_{SS} + 0.3$	V	CMOS Hysteresis
		DEBUG		V _{SS}		+ 0.3		input
	$V_{\rm ILD}$	I/F	-	- 0.3	-	0.8	V	TTL Input
		1/1	$4.5V \le V_{CC} \le 5.5V$	- 0.5				
		4mA	$I_{OH} = -4mA$	V _{CC}				
	V_{OH4}	type	$2.7V \le V_{CC} < 4.5V$	- 0.5	-	V_{CC}	V	
"H" level		-7 F -	$I_{OH} = -1.5 \text{mA}$					
output			$4.5 \text{V} \le \text{V}_{\text{CC}} \le 5.5 \text{V}$					
voltage	* 7	2 4	$I_{OH} = -3 \text{mA}$	V_{CC}		X 7	* 7	
	V_{OH3}	3mA type	$2.7V \le V_{CC} < 4.5V$	- 0.5	-	V_{CC}	V	
			$I_{OH} = -1.5 \text{mA}$					
			$4.5V \le V_{CC} \le 5.5V$					
	V	4mA	$I_{OL} = +4mA$			0.4	V	
"I " level	V_{OL4}	type	$2.7V \leq V_{CC} < 4.5V$	_	-	0.4	*	
$\begin{array}{c c} \text{"L" level} \\ \text{output} \\ \text{voltage} & V_{\text{OL3}} \end{array}$			$I_{OL} = +1.7 \text{mA}$					
	Vora	3mA type	$2.7V \le V_{CC} < 5.5V$	_		0.4	V	
Tomage	voltage V _{OL3}		$I_{OL} = +3mA$			0.7		
	V_{OLD}	DEBUG	$V_{\rm CC} = 2.7 V$	0		0.25	V	
	, OLD	I/F	$I_{OL} = +25 \text{mA}$			0.25		

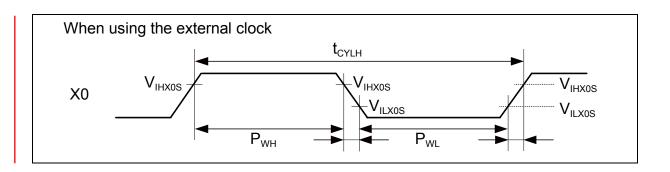
Darameter	Cymbol	Din nama	Conditions		Value		Unit	Remarks
Parameter	Symbol	Pin name	Conditions	Min	Тур	Max	Offic	Remarks
Input leak current	${ m I}_{ m IL}$	Pnn_m	$egin{aligned} V_{SS} < V_I < V_{CC} \ AV_{SS} < V_I < \ AV_{CC}, AVRH \end{aligned}$	- 1	-	+ 1	μΑ	
Pull-up resistance value	R_{PU}	Pnn_m	$V_{CC} = 5.0V \pm 10\%$	25	50	100	kΩ	
Input capacitance	$C_{ m IN}$	Other than C, Vcc, Vss, AVcc, AVss, AVRH	-	-	5	15	pF	

4. AC Characteristics

(1) Main Clock Input Characteristics

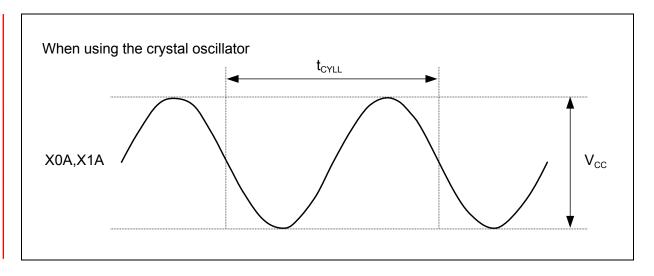
·		Pin	.51, 15-	Value	7 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1		$7, 1_{A} = -40^{\circ} \text{C to} + 125^{\circ} \text{C}$
Parameter	Symbol	name	Min	Тур	Max	Unit	Remarks
			4	-	8	MHz	When using a crystal oscillator, PLL off
Input frequency	f_{C}	X0, X1	1	-	8	MHz	When using an opposite phase external clock, PLL off
			4	-	8	MHz	When using a crystal oscillator or opposite phase external clock, PLL on
Input for guaran	£	X0	ı	-	8	MHz	When using a single phase external clock in "Fast Clock Input mode", PLL off
Input frequency	f _{FCI}	Α0	4	-	8	MHz	When using a single phase external clock in "Fast Clock Input mode", PLL on
Input clock cycle	t _{CYLH}	-	125	-	-	ns	
Input clock pulse width	P_{WH}, P_{WL}	-	55	-	-	ns	

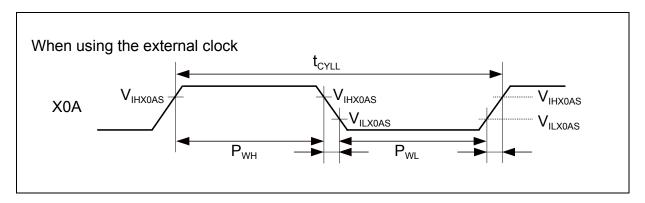




(2) Sub Clock Input Characteristics

		($V_{CC} = AV_{CC} = 2$	2.7V to 5	$5.5V$, $V_{SS} =$	$AV_{SS} =$	0V, T _A	$= -40^{\circ}\text{C to} + 125^{\circ}\text{C}$
Parameter	Symbol	Pin	Conditions		Value		Unit	Remarks
Parameter	Syllibol	name	Conditions	Min	Тур	Max	Ullit	Remarks
		VOA	-	ı	32.768	ı	kHz	When using an oscillation circuit
Input frequency	frequency f_{CL}	f_{CL} $X0A, X1A$	-	ı	ı	100	kHz	When using an opposite phase external clock
		X0A	-	ı	ı	50	kHz	When using a single phase external clock
Input clock cycle	$t_{ m CYLL}$	-	-	10	-	-	μs	
Input clock pulse width	-	-	$P_{WH}/t_{CYLL}, \\ P_{WL}/t_{CYLL}$	30	-	70	%	





(3) Built-in RC Oscillation Characteristics

 $(V_{CC} = AV_{CC} = 2.7V \text{ to } 5.5V, V_{SS} = AV_{SS} = 0V, T_A = -40^{\circ}\text{C to} + 125^{\circ}\text{C})$

Daramatar	Symbol	(,,,,	Value		l loit	,
Parameter	Symbol	Min	Тур	Max	Unit	Remarks
Cleak fraguency	t	50	100	200	kHz	When using slow frequency of RC oscillator
Clock frequency	f_{RC}	1	2	4	MHz	When using fast frequency of RC oscillator
RC clock stabilization		80	160	320	μs	When using slow frequency of RC oscillator (16 RC clock cycles)
time	t _{RCSTAB}	64	128	256	μs	When using fast frequency of RC oscillator (256 RC clock cycles)

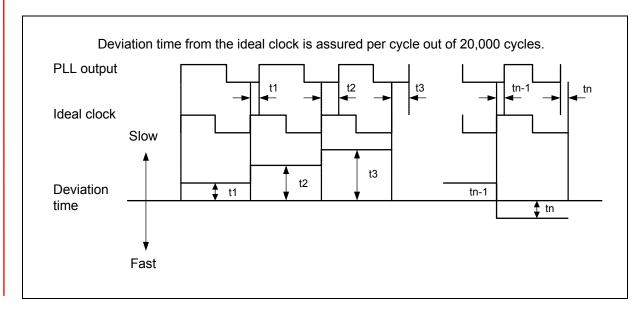
(4) Internal Clock Timing

Parameter	Cumbal	Va	Linit	
Parameter	Symbol	Min	Max	Unit
Internal System clock frequency (CLKS1 and CLKS2)	f_{CLKS1}, f_{CLKS2}	-	54	MHz
Internal CPU clock frequency (CLKB), Internal peripheral clock frequency (CLKP1)	f_{CLKB}, f_{CLKP1}	-	32	MHz
Internal peripheral clock frequency (CLKP2)	f_{CLKP2}	-	32	MHz

(5) Operating Conditions of PLL

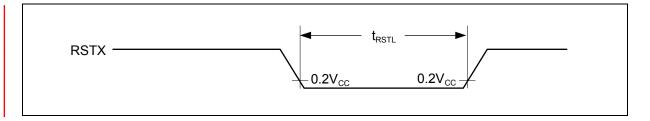
 $(V_{CC}=A\underline{V_{CC}}=2.7V$ to 5.5V, $V_{SS}=AV_{SS}=0V,\,T_A$ = - 40°C to + 125°C)

Parameter	Symbol	Value			Unit	Remarks	
Faranteter	Symbol	Min	Тур	Max	5	Remarks	
PLL oscillation stabilization wait time	t_{LOCK}	1	-	4	ms	For CLKMC = 4MHz	
PLL input clock frequency	f_{PLLI}	4	-	8	MHz		
PLL oscillation clock frequency	f_{CLKVCO}	56	-	108	MHz	Permitted VCO output frequency of PLL (CLKVCO)	
PLL phase jitter	t _{PSKEW}	-5	-	+5	ns	For CLKMC (PLL input clock) ≥ 4MHz	



(6) Reset Input

Parameter	Symbol	Pin name	Va	Unit		
i arameter	Gyrribor	1 III Hairie	Min	Max	Offic	
Reset input time		D CITY	10	-	μs	
Rejection of reset input time	$t_{ m RSTL}$	RSTX	1	-	μs	

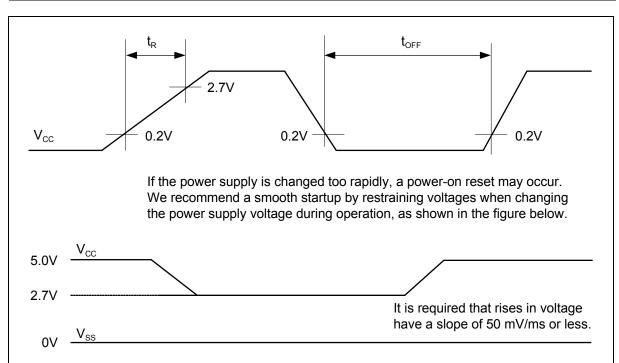


(7) Power-on Reset Timing

 $(V_{CC} = AV_{CC} = 2.7V \text{ to } 5.5V, V_{SS} = AV_{SS} = 0V, T_A = -40^{\circ}\text{C to} + 125^{\circ}\text{C})$

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Parameter	Symbol	Din nama		Value	Unit		
Parameter	Symbol	Pin name	Min	Тур	Max	Offic	
Power on rise time	t_{R}	Vcc	0.05	-	30	ms	
Power off time	t _{OFF}	Vcc	1	-	-	ms	



46

(8) USART Timing

 $(V_{CC} = AV_{CC} = 2.7V \text{ to } 5.5V, V_{SS} = AV_{SS} = 0V, T_A = -40^{\circ}\text{C to } + 125^{\circ}\text{C}, C_L = 50 \text{pF})$

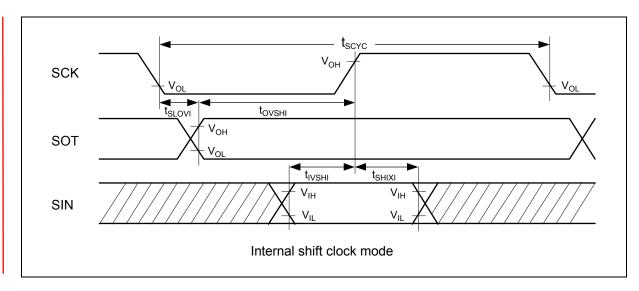
		Pin	Conditions	4.5V ≤ V _C				
Parameter	Symbol	name	Conditions	Min	Max	Min	Max	Unit
Serial clock cycle time	t_{SCYC}	SCKn		4t _{CLKP1}	-	4t _{CLKP1}	1	ns
$SCK \downarrow \rightarrow SOT$ delay time	$t_{ m SLOVI}$	SCKn, SOTn		- 20	+ 20	- 30	+ 30	ns
$SOT \rightarrow SCK \uparrow delay time$	t _{OVSHI}	SCKn, SOTn	Internal shift clock mode	$N \times t_{CLKP1} - 20^*$	-	$N \times t_{CLKP1}$ -30^*	-	ns
$SIN \rightarrow SCK \uparrow setup time$	t _{IVSHI}	SCKn, SINn		t _{CLKP1} + 45	-	t _{CLKP1} + 55	-	ns
$SCK \uparrow \rightarrow SIN \text{ hold time}$	t _{SHIXI}	SCKn, SINn		0	-	0	-	ns
Serial clock "L" pulse width	t _{SLSH}	SCKn		t _{CLKP1} + 10	-	t _{CLKP1} + 10	-	ns
Serial clock "H" pulse width	t _{SHSL}	SCKn		t _{CLKP1} + 10	-	t _{CLKP1} + 10	-	ns
$SCK \downarrow \rightarrow SOT$ delay time	t _{SLOVE}	SCKn, SOTn		1	2t _{CLKP1} + 45	-	2t _{CLKP1} + 55	ns
$SIN \rightarrow SCK \uparrow setup time$	t _{IVSHE}	SCKn, SINn	External shift clock mode	t _{CLKP1} /2 + 10	-	t _{CLKP1} /2 + 10	1	ns
$SCK \uparrow \rightarrow SIN \text{ hold time}$	t _{SHIXE}	SCKn, SINn		t _{CLKP1} + 10	-	t _{CLKP1} + 10	-	ns
SCK fall time	t_{F}	SCKn		-	20	-	20	ns
SCK rise time	t_{R}	SCKn		-	20	-	20	ns

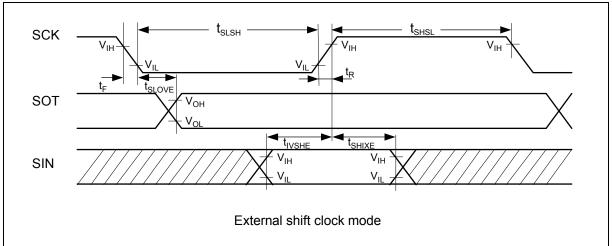
Notes:

- AC characteristic in CLK synchronized mode.
- C_L is the load capacity value of pins when testing.
- Depending on the used machine clock frequency, the maximum possible baud rate can be limited by some parameters. These parameters are shown in "MB96600 series HARDWARE MANUAL".
- t_{CLKP1} indicates the peripheral clock 1 (CLKP1), Unit: ns
- These characteristics only guarantee the same relocate port number. For example, the combination of SCKn and SOTn R is not guaranteed.
- $\ast :$ Parameter N depends on t_{SCYC} and can be calculated as follows:
 - If $t_{SCYC} = 2 \times k \times t_{CLKP1}$, then N = k, where k is an integer > 2
 - \bullet If $t_{SCYC}\!=(2\times k+1)\times t_{CLKP1},$ then N=k+1, where k is an integer >1

Examples:

t _{SCYC}	N
$4 \times t_{CLKP1}$	2
$5 \times t_{\text{CLKP1}}, 6 \times t_{\text{CLKP1}}$	3
$7 \times t_{\text{CLKP1}}, 8 \times t_{\text{CLKP1}}$	4



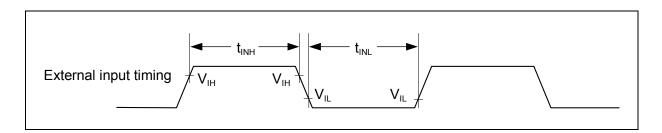


48

(9) External Input Timing

Parameter	Symbol	Pin name	Value		Unit	Remarks										
Parameter	Symbol	riii iiaiiie	Min	Max	Ullit	Remarks										
		Pnn_m				General Purpose I/O										
		ADTG				A/D Converter trigger input										
		TINn				Reload Timer										
		TTGn	2t _{CLKP1} +200			PPG trigger input										
	t _{INH} , t _{INL}					FRCKn,	$(t_{CLKP1} =$	-	ns	Free-Running Timer						
Input pulse width							FRCKn_R	1/f _{CLKP1})*			input clock					
input puise width							t_{INL}	$t_{ m INL}$	$t_{ m INL}$	$t_{ m INL}$	$t_{ m INL}$	$t_{ m INL}$	$t_{ m INL}$	$t_{ m INL}$	$t_{ m INL}$	$t_{ m INL}$
		AINn,				Quadrature										
		BINn,				Position/Revolution										
		ZINn				Counter										
		INTn, INTn_R				External Interrupt										
		NMI	200	-	ns	Non-Maskable										
						Interrupt										

^{*:} t_{CLKP1} indicates the peripheral clock1 (CLKP1) cycle time except stop when in stop mode.

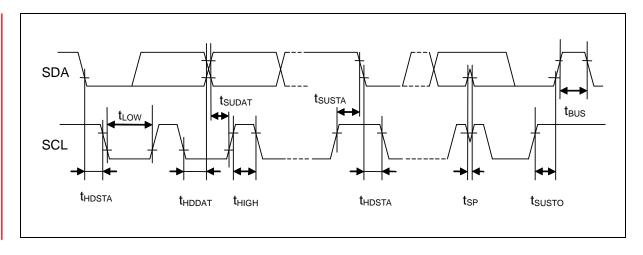


(10) I²C Timing

Parameter	Symbol	Conditions	Typica	Typical mode		High-speed mode*4		
			Min	Max	Min	Max		
SCL clock frequency	f_{SCL}		0	100	0	400	kHz	
(Repeated) START condition								
hold time	t_{HDSTA}		4.0	-	0.6	-	μs	
$SDA \downarrow \rightarrow SCL \downarrow$								
SCL clock "L" width	t_{LOW}		4.7	-	1.3	-	μs	
SCL clock "H" width	t _{HIGH}		4.0	-	0.6	-	μs	
(Repeated) START condition								
setup time	t_{SUSTA}		4.7	-	0.6	-	μs	
$SCL \uparrow \rightarrow SDA \downarrow$		$C_{L} = 50 pF,$ $R = (Vp/I_{OL})^{*1}$						
Data hold time	t	$R = (Vp/I_{OL})^{*1}$	0	3.45* ²	0	$0.9*^3$	μs	
$SCL \downarrow \rightarrow SDA \downarrow \uparrow$	t _{HDDAT}		0 3.43	3.43	, °	0.7	μs	
Data setup time	$t_{ m SUDAT}$		250	_	100	_	ns	
$SDA \downarrow \uparrow \rightarrow SCL \uparrow$	SUDAI		230	_	100	_	113	
STOP condition setup time	t_{SUSTO}		4.0	_	0.6	_	μs	
$SCL \uparrow \rightarrow SDA \uparrow$	SUSTO		7.0		0.0		μδ	
Bus free time between								
"STOP condition" and	$t_{ m BUS}$		4.7	-	1.3	-	μs	
"START condition"								
Pulse width of spikes which	4		0	(1-1.5) ×	0	(1-1.5) ×		
will be suppressed by input noise filter	t_{SP}	-	0	t _{CLKP1} *5	0	t _{CLKP1} *5	ns	

^{*1:} R and C_L represent the pull-up resistance and load capacitance of the SCL and SDA lines, respectively. Vp indicates the power supply voltage of the pull-up resistance and I_{OL} indicates V_{OL} guaranteed current.

^{*5:} t_{CLKP1} indicates the peripheral clock1 (CLKP1) cycle time.



^{*2:} The maximum t_{HDDAT} only has to be met if the device does not extend the "L" width (t_{LOW}) of the SCL signal.

^{*3:} A high-speed mode I^2C bus device can be used on a standard mode I^2C bus system as long as the device satisfies the requirement of " $t_{SUDAT} \ge 250 ns$ ".

^{*4:} For use at over 100kHz, set the peripheral clock1 (CLKP1) to at least 6MHz.

5. A/D Converter

(1) Electrical Characteristics for the A/D Converter

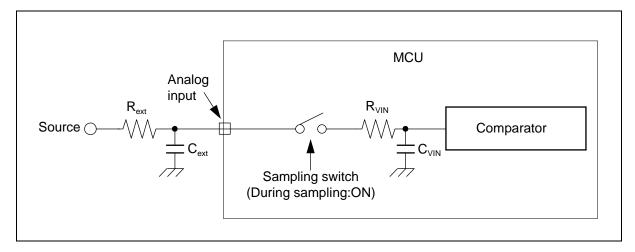
Doromotor	Cymbol	Pin		Value		Unit	Domarka
Parameter	Symbol	name	Min	Тур	Max	Unit	Remarks
Resolution	-	-	-	-	10	bit	
Total error	-	-	- 3.0	-	+ 3.0	LSB	
Nonlinearity error	-	-	- 2.5	-	+ 2.5	LSB	
Differential Nonlinearity error	-	-	- 1.9	-	+ 1.9	LSB	
Zero transition voltage	V _{OT}	ANn	Typ - 20	AV _{SS} +0.5LSB	Typ + 20	mV	
Full scale transition voltage	V_{FST}	ANn	Typ - 20	AVRH - 1.5LSB	Typ + 20	mV	
Compare time*	-		1.0	-	5.0	μs	$4.5V \le AV_{CC} \le 5.5V$
Compare time	-	-	2.2	-	8.0	μs	$2.7V \le AV_{CC} < 4.5V$
Sampling time*	_		0.5	-	-	μs	$4.5V \le AV_{CC} \le 5.5V$
Sampling time	-	-	1.2	-	-	μs	$2.7V \le AV_{CC} < 4.5V$
Power supply	I_A		-	2.0	3.1	mA	A/D Converter active
current	I_{AH}	AV_{CC}	-	-	3.3	μΑ	A/D Converter not operated
Reference power supply current	I_R	AVRH	-	520	810	μΑ	A/D Converter active
(between AVRH and AV _{SS})	I_{RH}	AVKH	-	-	1.0	μΑ	A/D Converter not operated
Analog input capacity	C_{VIN}	ANn	-	-	15.9	pF	
Analaa immadanaa	D	ANn	-	-	2050	Ω	$4.5V \le AV_{CC} \le 5.5V$
Analog impedance	$R_{ m VIN}$	AINII	-	-	3600	Ω	$2.7V \le AV_{CC} < 4.5V$
Analog port input current (during conversion)	I _{AIN}	ANn	- 0.3	-	+ 0.3	μА	$\begin{array}{l} AV_{SS} < V_{AIN} < \\ AV_{CC}, AVRH \end{array}$
Analog input voltage	V _{AIN}	ANn	AV_{SS}	-	AVRH	V	
Reference voltage range	-	AVRH	AV _{CC} - 0.1	-	AV_{CC}	V	
Variation between channels	-	ANn	-	-	4.0	LSB	

^{*:} Time for each channel.

(2) Accuracy and Setting of the A/D Converter Sampling Time

If the external impedance is too high or the sampling time too short, the analog voltage charged to the internal sample and hold capacitor is insufficient, adversely affecting the A/D conversion precision.

To satisfy the A/D conversion precision, a sufficient sampling time must be selected. The required sampling time (Tsamp) depends on the external driving impedance R_{ext} , the board capacitance of the A/D converter input pin C_{ext} and the AV_{CC} voltage level. The following replacement model can be used for the calculation:



R_{ext}: External driving impedance

Cext: Capacitance of PCB at A/D converter input

C_{VIN}: Analog input capacity (I/O, analog switch and ADC are contained)

R_{VIN}: Analog input impedance (I/O, analog switch and ADC are contained)

The following approximation formula for the replacement model above can be used: $Tsamp = 7.62 \times (Rext \times Cext + (Rext + R_{VIN}) \times C_{VIN})$

- Do not select a sampling time below the absolute minimum permitted value. (0.5 μ s for 4.5 V \leq AV_{CC} \leq 5.5 V, 1.2 μ s for 2.7 V \leq AV_{CC} < 4.5 V)
- If the sampling time cannot be sufficient, connect a capacitor of about $0.1\mu F$ to the analog input pin.
- A big external driving impedance also adversely affects the A/D conversion precision due to the pin input leakage current IIL (static current before the sampling switch) or the analog input leakage current IAIN (total leakage current of pin input and comparator during sampling). The effect of the pin input leakage current IIL cannot be compensated by an external capacitor.
- The accuracy gets worse as |AVRH AV_{SS}| becomes smaller.

(3) Definition of A/D Converter Terms

• Resolution : Analog variation that is recognized by an A/D converter.

• Nonlinearity error : Deviation of the actual conversion characteristics from a straight line that connects

the zero transition point (0b00000000000 \longleftrightarrow 0b0000000001) to the full-scale

transition point (0b11111111110 $\leftarrow \rightarrow$ 0b1111111111).

• Differential nonlinearity error : Deviation from the ideal value of the input voltage that is required to

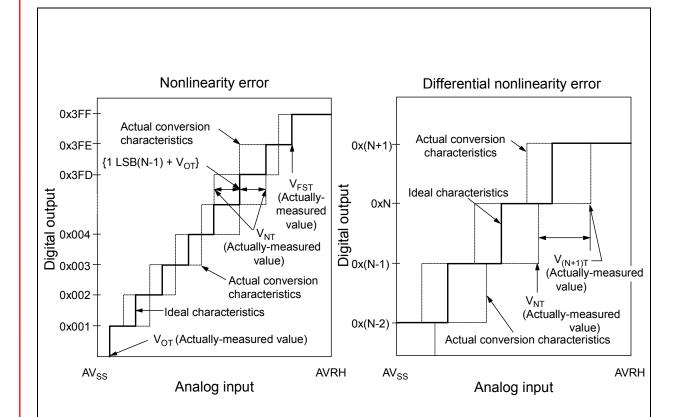
change the output code by 1LSB.

•Total error : Difference between the actual value and the theoretical value. The total error

includes zero transition error, full-scale transition error and nonlinearity error.

• Zero transition voltage: Input voltage which results in the minimum conversion value.

• Full scale transition Voltage: Input voltage which results in the maximum conversion value.



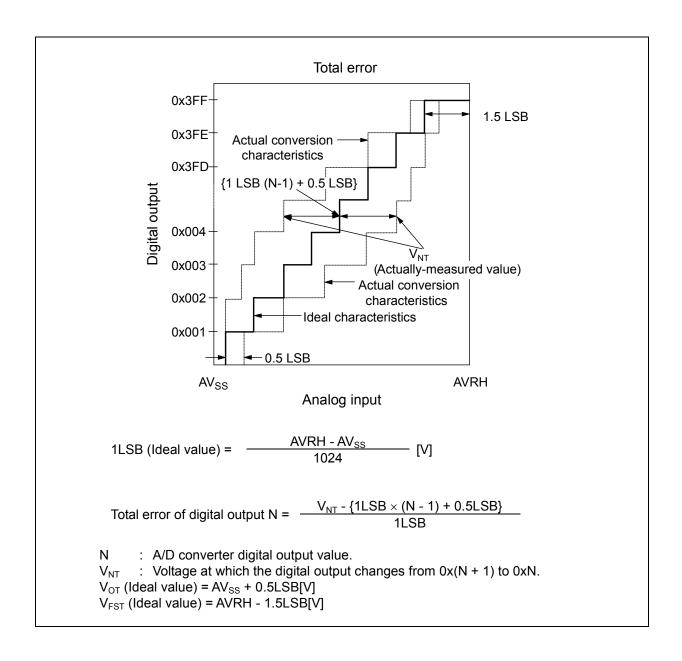
Nonlinearity error of digital output N =
$$\frac{V_{NT} - \{1LSB \times (N-1) + V_{OT}\}}{1LSB}$$
 [LSB]

Differential nonlinearity error of digital output N =
$$\frac{V_{(N+1)T} - V_{NT}}{1LSB}$$
 - 1 [LSB]

$$1LSB = \frac{V_{FST} - V_{OT}}{1022}$$

N : A/D converter digital output value.

 $\begin{array}{lll} V_{OT} & : & \text{Voltage at which the digital output changes from } 0x000 \text{ to } 0x001. \\ V_{FST} & : & \text{Voltage at which the digital output changes from } 0x3FE \text{ to } 0x3FF. \\ V_{NT} & : & \text{Voltage at which the digital output changes from } 0x(N-1) \text{ to } 0xN. \\ \end{array}$

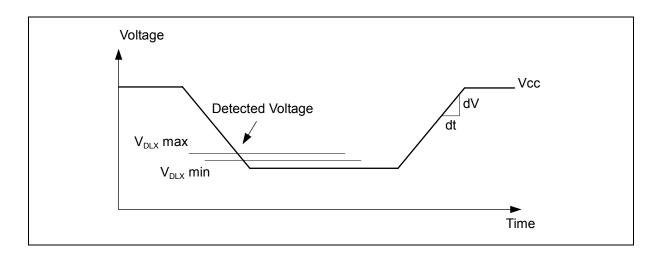


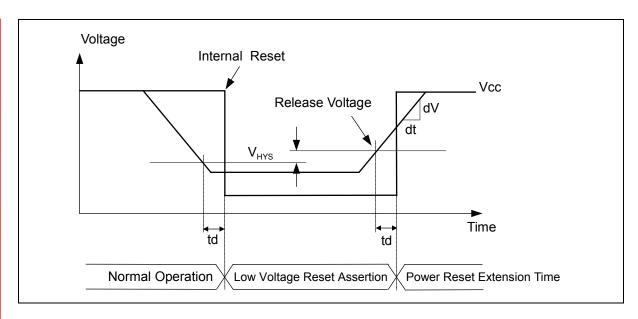
6. Low Voltage Detection Function Characteristics

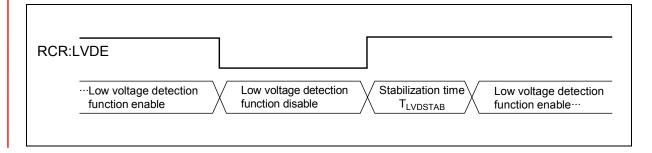
Parameter		Conditions		Value			
Farameter	Symbol	Conditions	Min	Тур	Max	Unit	
	V_{DL0}	$CILCR:LVL = 0000_B$	2.70	2.90	3.10	V	
	V_{DL1}	$CILCR:LVL = 0001_B$	2.79	3.00	3.21	V	
	V_{DL2}	$CILCR:LVL = 0010_B$	2.98	3.20	3.42	V	
Detected voltage*1	V_{DL3}	$CILCR:LVL = 0011_B$	3.26	3.50	3.74	V	
	V_{DL4}	$CILCR:LVL = 0100_B$	3.45	3.70	3.95	V	
	V_{DL5}	$CILCR:LVL = 0111_B$	3.73	4.00	4.27	V	
	V_{DL6}	$CILCR:LVL = 1001_B$	3.91	4.20	4.49	V	
Power supply voltage change rate*2	dV/dt	-	- 0.004	-	+ 0.004	V/µs	
Hystomosis width	V	CILCR:LVHYS=0	-	-	50	mV	
Hysteresis width	V_{HYS}	CILCR:LVHYS=1	80	100	120	mV	
Stabilization time	$T_{LVDSTAB}$	-	-	-	75	μs	
Detection delay time	t _d	-	-	-	30	μs	

^{*1:} If the power supply voltage fluctuates within the time less than the detection delay time (t_d), there is a possibility that the low voltage detection will occur or stop after the power supply voltage passes the detection range.

^{*2:} In order to perform the low voltage detection at the detection voltage (V_{DLX}) , be sure to suppress fluctuation of the power supply voltage within the limits of the change ration of power supply voltage.







7. Flash Memory Write/Erase Characteristics

 $(V_{CC} = AV_{CC} = 2.7V \text{ to } 5.5V, V_{SS} = AV_{SS} = 0V, T_A = -40^{\circ}\text{C to} + 125^{\circ}\text{C})$

Parameter		Conditions	Value		Unit	Remarks	
Faiai	iletei	Conditions	Min	Тур	Max	5	Remarks
	Large Sector	$T_A \le +105^{\circ}C$	-	1.6	7.5	S	
Sector erase time	Small Sector	-	-	0.4	2.1	S	Includes write time prior to internal erase.
	Security Sector	-	-	0.31	1.65	S	
Word (16-bit)	Large Sector	T _A ≤+ 105°C	-	25	400	μs	Not including system-level overhead
write time	Small Sector	-	-	25	400	μs	time.
Chip erase time		T _A ≤+105°C	-	11.51	55.05	S	Includes write time prior to internal erase.

Note: While the Flash memory is written or erased, shutdown of the external power (V_{CC}) is prohibited. In the application system where the external power (V_{CC}) might be shut down while writing or erasing, be sure to turn the power off by using a low voltage detection function.

To put it concrete, change the external power in the range of change ration of power supply voltage $(-0.004 \text{V/}\mu\text{s} \text{ to } +0.004 \text{V/}\mu\text{s})$ after the external power falls below the detection voltage $(V_{DLX})^{*1}$.

Write/Erase cycles and data hold time

Write/Erase cycles	Data hold time
(cycle)	(year)
1,000	20 *2
10,000	10 *2
100,000	5 *2

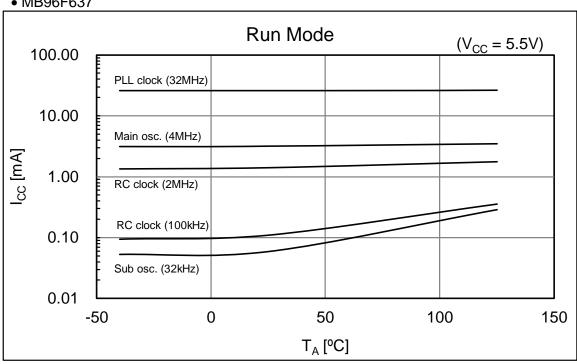
^{*1:} See "6. Low Voltage Detection Function Characteristics".

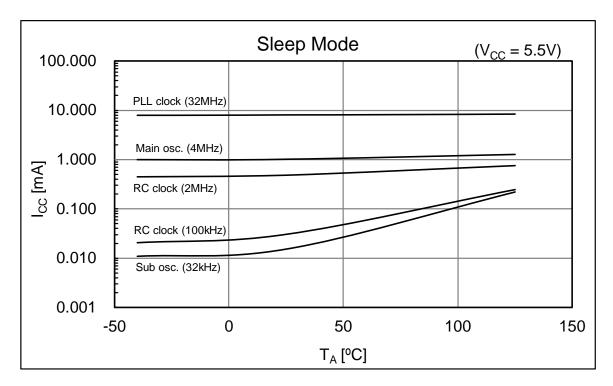
^{*2:} This value comes from the technology qualification (using Arrhenius equation to translate high temperature measurements into normalized value at $+85^{\circ}$ C).

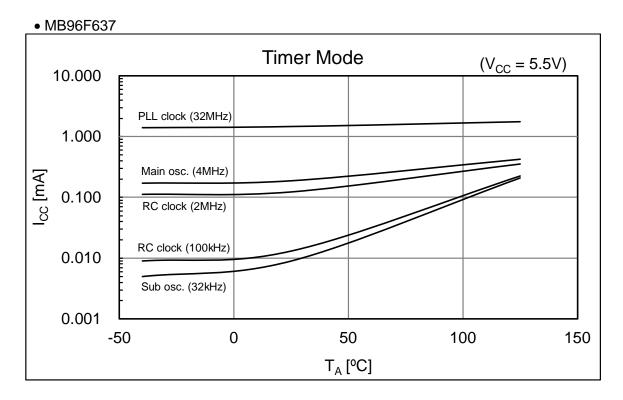
■ EXAMPLE CHARACTERISTICS

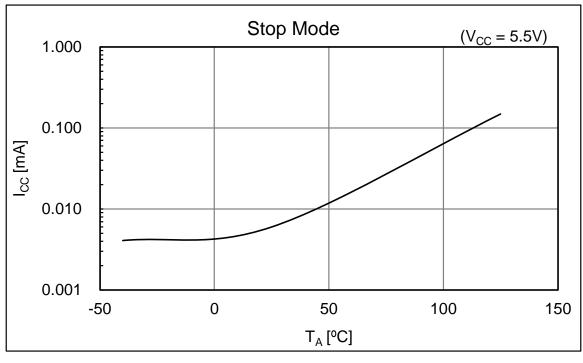
This characteristic is an actual value of the arbitrary sample. It is not the guaranteed value.

• MB96F637









• Used setting

Mode	Selected Source Clock	Clock/Regulator and FLASH Settings
Run mode	PLL	CLKS1 = CLKS2 = CLKB = CLKP1 = CLKP2 = 32MHz
	Main osc.	CLKS1 = CLKS2 = CLKB = CLKP1 = CLKP2 = 4MHz
	RC clock fast	CLKS1 = CLKS2 = CLKB = CLKP1 = CLKP2 = 2MHz
	RC clock slow	CLKS1 = CLKS2 = CLKB = CLKP1 = CLKP2 = 100kHz
	Sub osc.	CLKS1 = CLKS2 = CLKB = CLKP1 = CLKP2 = 32kHz
Sleep mode	PLL	CLKS1 = CLKS2 = CLKP1 = CLKP2 = 32MHz
Sicep mode	I LL	Regulator in High Power Mode,
		(CLKB is stopped in this mode)
	Main osc.	CLKS1 = CLKS2 = CLKP1 = CLKP2 = 4MHz
		Regulator in High Power Mode,
		(CLKB is stopped in this mode)
	RC clock fast	CLKS1 = CLKS2 = CLKP1 = CLKP2 = 2MHz
		Regulator in High Power Mode,
		(CLKB is stopped in this mode)
	RC clock slow	CLKS1 = CLKS2 = CLKP1 = CLKP2 = 100kHz
		Regulator in Low Power Mode,
	G 1	(CLKB is stopped in this mode)
	Sub osc.	CLKS1 = CLKS2 = CLKP1 = CLKP2 = 32kHz
		Regulator in Low Power Mode,
Timer mode	PLL	(CLKB is stopped in this mode) CLKMC = 4MHz, CLKPLL = 32MHz
Timer mode	FLL	(System clocks are stopped in this mode)
		Regulator in High Power Mode,
		FLASH in Power-down / reset mode
	Main osc.	CLKMC = 4MHz
		(System clocks are stopped in this mode)
		Regulator in High Power Mode,
		FLASH in Power-down / reset mode
	RC clock fast	CLKMC = 2MHz
		(System clocks are stopped in this mode)
		Regulator in High Power Mode,
		FLASH in Power-down / reset mode
	RC clock slow	CLKMC = 100kHz
		(System clocks are stopped in this mode)
		Regulator in Low Power Mode,
	Cultura	FLASH in Power-down / reset mode
	Sub osc.	CLKMC = 32 kHz (System clocks are stopped in this mode)
		Regulator in Low Power Mode,
		FLASH in Power-down / reset mode
Stop mode	stopped	(All clocks are stopped in this mode)
Stop mode	stopped	Regulator in Low Power Mode,
		FLASH in Power-down / reset mode

■ ORDERING INFORMATION

MCU with CAN controller

Part number	Flash memory	Package*
MB96F633RBPMC-GSE1	Flash A	80-pin plastic LQFP
MB96F633RBPMC-GSE2	(96.5KB)	(FPT-80P-M21)
MB96F635RBPMC-GSE1	Flash A	80-pin plastic LQFP
MB96F635RBPMC-GSE2	(160.5KB)	(FPT-80P-M21)
MB96F636RBPMC-GSE1	Flash A	80-pin plastic LQFP
MB96F636RBPMC-GSE2	(288.5KB)	(FPT-80P-M21)
MB96F637RBPMC-GSE1	Flash A	80-pin plastic LQFP
MB96F637RBPMC-GSE2	(416.5KB)	(FPT-80P-M21)

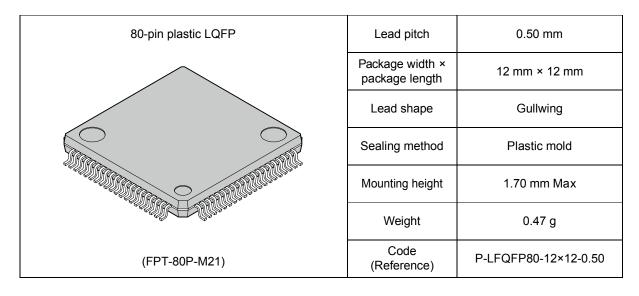
^{*:} For details about package, see "■PACKAGE DIMENSION".

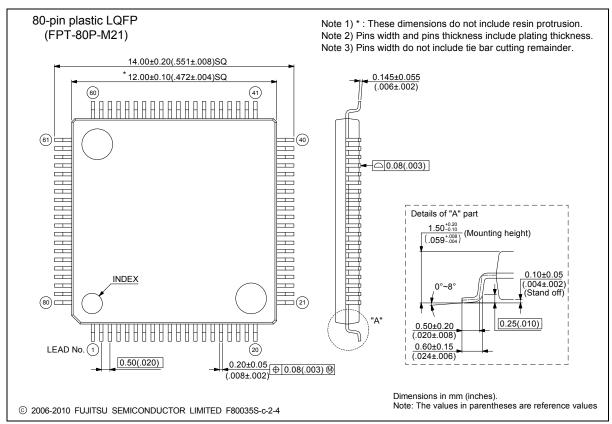
MCU without CAN controller

Part number	Flash memory	Package*
MB96F633ABPMC-GSE1	Flash A	80-pin plastic LQFP
MB96F633ABPMC-GSE2	(96.5KB)	(FPT-80P-M21)
MB96F635ABPMC-GSE1	Flash A	80-pin plastic LQFP
MB96F635ABPMC-GSE2	(160.5KB)	(FPT-80P-M21)

^{*:} For details about package, see "■PACKAGE DIMENSION".

■ PACKAGE DIMENSION





Please check the latest package dimension at the following URL. http://edevice.fujitsu.com/package/en-search/

■ MAJOR CHANGES IN THIS EDITION

A change on a page is indicated by a vertical line drawn on the left side of that page.

Seature Feature Feature Feature Feature Feature Feature Feature Feature Changed the description of "External Interrupts" Interrupt mask and pending bit per channel Feature Interrupt mask bit per channel Feature Feat	Page	Section	Change Results
Up to 16 MHz external clock for devices with fast clofeature Up to 8 MHz external clock for devices with fast clofeature Changed the description of "External Interrupts" Interrupt mask and pending bit per channel Interrupt mask bit per channel Changed the description of "Built-in On Chip Debugg Event sequencer: 2 levels Event sequencer: 2 levels + reset Added the Product Changed the Remark of RLT RLT 0/1/6 Only RLT6 can be used as PPG clock sour RLT 0/1/6 BLOCK DIAGRAM Deleted the block of RLT6 from PPG block Changed the RLT block 2ch O/1/6 3ch PIN DESCRIPTION Changed the Description of PPGn_B Programmable Pulse Generator n output (8bit) Programmable Pulse Generator n output (16bit/8bit) Changed the Remarks of type B Changed the Remarks of type B Changed the Remarks of type B CCMOS hysteresis input with input shutdown function lo _L = 4mA, I _{OH} = -4mA, Programmable pull-up resist of CCMOS level output (I _{OL} = 4mA, I _{OH} = -4mA), Auton input with input shutdown function and programmable resistor)	-	-	PRELIMINARY → Data sheet
Seature Changed the description of "External Interrupts" Interrupt mask and pending bit per channel		■FEATURES	Up to 16 MHz external clock for devices with fast clock input feature
Interrupt mask and pending bit per channel Interrupt mask bit per channel Changed the description of "Built-in On Chip Debugg - Event sequencer: 2 levels - Event sequencer: 2 levels + reset Added the Product Changed the Remark of RLT RLT 0/1/6 Only RLT6 can be used as PPG clock sour RLT 0/1/6 Only RLT6 can be used as PPG clock sour RLT 0/1/6 Only RLT6 from PPG block Changed the RLT block 2ch - 0/1/6 3ch PIN DESCRIPTION Changed the Description of PPGn_B Programmable Pulse Generator n output (8bit) - Programmable Pulse Generator n output (16bit/8bit) Changed the Remarks of type B Changed the Remarks of type B Changed the Remarks of type B (CMOS hysteresis input with input shutdown function IoL = 4mA, IoH = -4mA, Programmable pull-up resist - (CMOS level output (IoL = 4mA, IoH = -4mA), Auton input with input shutdown function and programmabl resistor)			Up to 8 MHz external clock for devices with fast clock input feature
Changed the description of "Built-in On Chip Debugg - Event sequencer: 2 levels → - Event sequencer: 2 levels + reset Added the Product Changed the Remark of RLT RLT 0/1/6 Only RLT6 can be used as PPG clock sour → RLT 0/1/6 BBLOCK DIAGRAM Deleted the block of RLT6 from PPG block Changed the RLT block 2ch → 0/1/6 3ch PPIN DESCRIPTION Changed the Description of PPGn_B Programmable Pulse Generator n output (8bit) → Programmable Pulse Generator n output (16bit/8bit) Changed the Remarks of type B Changed the Remarks of type B (CMOS hysteresis input with input shutdown function IoL = 4mA, IoH = -4mA, Programmable resistor)			Interrupt mask and pending bit per channel
Changed the description of "Built-in On Chip Debugg - Event sequencer: 2 levels - Event sequencer: 2 levels + reset Added the Product Changed the Remark of RLT RLT 0/1/6 Only RLT6 can be used as PPG clock sour - RLT 0/1/6 BLOCK DIAGRAM Deleted the block of RLT6 from PPG block Changed the RLT block 2ch - 0/1/6 3ch PIN DESCRIPTION Changed the Description of PPGn_B Programmable Pulse Generator n output (8bit) - Programmable Pulse Generator n output (16bit/8bit) Changed the Remarks of type B Changed the Remarks of type B (CMOS hysteresis input with input shutdown function log_ 4mA, I _{OH} = -4mA, Programmable pull-up resist - (CMOS level output (I _{OL} = 4mA, I _{OH} = -4mA), Auton input with input shutdown function and programmabl resistor)	4		Interrupt mask bit per channel
Added the Product Changed the Remark of RLT RLT 0/1/6 Only RLT6 can be used as PPG clock sour RLT 0/1/6 BLOCK DIAGRAM Deleted the block of RLT6 from PPG block Changed the RLT block 2ch 0/1/6 3ch PIN DESCRIPTION Changed the Description of PPGn_B Programmable Pulse Generator n output (8bit) Programmable Pulse Generator n output (16bit/8bit) Changed the Remarks of type B Changed the Remarks of type B (CMOS hysteresis input with input shutdown function IoL = 4mA, IoH = -4mA, Programmable pulse up to the programmable pulse up to the programmable pulse up resisted. (CMOS level output (IoL = 4mA, IoH = -4mA), Auton input with input shutdown function and programmable resistor)	4		\rightarrow
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RLT 0/1/6 Only RLT6 can be used as PPG clock sour RLT 0/1/6 ■BLOCK DIAGRAM Deleted the block of RLT6 from PPG block Changed the RLT block 2ch → 0/1/6 3ch ■PIN DESCRIPTION Changed the Description of PPGn_B Programmable Pulse Generator n output (8bit) → Programmable Pulse Generator n output (16bit/8bit) Changed the figure of type B Changed the Remarks of type B (CMOS hysteresis input with input shutdown function IoL = 4mA, IoH = -4mA, Programmable pull-up resist. → (CMOS level output (IoL = 4mA, IoH = -4mA), Auton input with input shutdown function and programmabl resistor)		■PRODUCT LINEUP	
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8 ■PIN DESCRIPTION Changed the Description of PPGn_B Programmable Pulse Generator n output (8bit) Programmable Pulse Generator n output (16bit/8bit) Changed the figure of type B Changed the Remarks of type B (CMOS hysteresis input with input shutdown function IoL = 4mA, IoH = -4mA, Programmable pull-up resisted (CMOS level output (IoL = 4mA, IoH = -4mA), Auton input with input shutdown function and programmable resistor)	6		2ch
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Programmable Pulse Generator n output (16bit/8bit) ■I/O CIRCUIT TYPE Changed the figure of type B Changed the Remarks of type B (CMOS hysteresis input with input shutdown function I _{OL} = 4mA, I _{OH} = -4mA, Programmable pull-up resistence of the company of	ı	■PIN DESCRIPTION	-
Changed the figure of type B Changed the Remarks of type B (CMOS hysteresis input with input shutdown function $I_{OL} = 4mA$, $I_{OH} = -4mA$, Programmable pull-up resisted (CMOS level output ($I_{OL} = 4mA$, $I_{OH} = -4mA$), Auton input with input shutdown function and programmable resistor)	8		
Changed the Remarks of type B (CMOS hysteresis input with input shutdown function I _{OL} = 4mA, I _{OH} = -4mA, Programmable pull-up resisted (CMOS level output (I _{OL} = 4mA, I _{OH} = -4mA), Auton input with input shutdown function and programmable resistor)			Programmable Pulse Generator n output (16bit/8bit)
(CMOS hysteresis input with input shutdown function $I_{OL} = 4mA$, $I_{OH} = -4mA$, Programmable pull-up resisted (CMOS level output ($I_{OL} = 4mA$, $I_{OH} = -4mA$), Auton input with input shutdown function and programmable resistor)		■I/O CIRCUIT TYPE	Changed the figure of type B
input with input shutdown function and programmabl resistor)	13		(CMOS hysteresis input with input shutdown function, $I_{OL} = 4\text{mA}$, $I_{OH} = -4\text{mA}$, Programmable pull-up resister) \rightarrow
Changed the figure of type G			(CMOS level output (I_{OL} = 4mA, I_{OH} = -4mA), Automotive input with input shutdown function and programmable pull-up resistor)
	14		Changed the figure of type G
17 ■ MEMORY MAP Changed the START addresses of Boot-ROM 0F:E000 _H → 0F:C000 _H		■MEMORY MAP	0F:E000 _H →

64

Page	Section	Change Results
	■USER ROM MEMORY MAP	Changed the annotation
	FOR FLASH DEVICES	Others (from DF:0200 _H to DF:1FFF _H) are all mirror area of
10		SAS-512B.
19		\rightarrow
		Others (from DF:0200 _H to DF:1FFF _H) is mirror area of
		SAS-512B.
	■INTERRUPT VECTOR	Changed the Description of CALLV0 to CALLV7
	TABLE	Reserved
		→ CALLY in the stift of
		CALLY instruction
		Changed the Description of RESET Reserved
		Reserved →
		Reset vector
21		Changed the Description of INT9
		Reserved
		\rightarrow
		INT9 instruction
		Changed the Description of EXCEPTION
		Reserved
		\rightarrow
		Undefined instruction execution
		Changed the Vector name of Vector number 64
		PPGRLT →
		RLT6
22		Changed the Description of Vector number 64
		Reload Timer 6 can be used as PPG clock source
		\rightarrow
		Reload Timer 6
25 . 20	■HANDLING PRECAUTIONS	Added a section
25 to 28		
	■HANDLING DEVICES	Added the description to "3. External clock usage"
		(3) Opposite phase external clock
		Changed the description in "7. Turn on sequence of power
30		supply to A/D converter and analog inputs"
		In this case, the voltage must not exceed AVRH or AV _{CC}
		→
		In this case, AVRH must not exceed AV _{CC} . Input voltage for
		ports shared with analog input ports also must not exceed AV_{CC}
21	1	
31		Added the description "12. Mode Pin (MD)"
33	■ELECTRICAL	Changed the annotation *4
	CHARACTERISTICS	Note that if the +B input is applied during power-on, the
	1. Absolute Maximum Ratings	power supply is provided from the pins and the resulting supply voltage may not be sufficient to operate the Power reset
		(except devices with persistent low voltage reset in internal
		vector mode).
		→ · · · · · · · · · · · · · · · · · · ·
		Note that if the +B input is applied during power-on, the
		power supply is provided from the pins and the resulting
		supply voltage may not be sufficient to operate the Power
		reset.

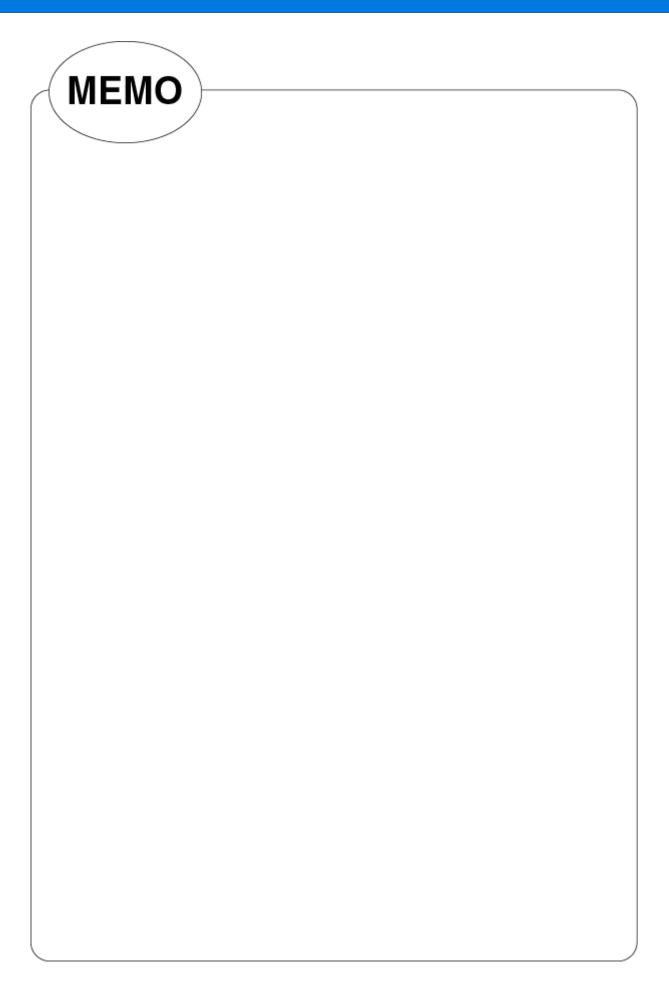
Page	Section	Change Results
rage	1. Absolute Maximum Ratings	Added the annotation *4
	1. Absolute Waximum Ratings	The DEBUG I/F pin has only a protective diode against V_{SS} .
		Hence it is only permitted to input a negative clamping current
33		(4mA). For protection against positive input voltages, use an
		external clamping diode which limits the input voltage to
		maximum 6.0V.
	2. Recommended Operating	Added the Value and Remarks to "Power supply voltage"
	Conditions	Min: 2.0V
		Typ: -
		Max: 5.5V
		Remarks: Maintains RAM data in stop mode
35		Changed the Value of "Smoothing capacitor at C pin"
		Typ: $1.0\mu\text{F} \rightarrow 1.0\mu\text{F}$ to $3.9\mu\text{F}$
		Max: $1.5\mu\text{F} \rightarrow 4.7\mu\text{F}$
		Changed the Remarks of "Smoothing capacitor at C pin"
		Deleted "(Target value)"
	3. DC Characteristics	Added "3.9μF (Allowance within ± 20%)" Deleted "(Target value)" from Remarks
	(1) Current Rating	· · · · · · · · · · · · · · · · · · ·
36	(1) Current Rating	Added the Symbol to "Power supply current in Run modes" I_{CCRCH} , I_{CCRCL}
		Changed the Conditions of I _{CCPLL} , I _{CCMAIN} , I _{CCSUB} in "Power supply current in Run modes"
		"Flash 0 wait" is added
		Changed the Value of "Power supply current in Run modes"
		I _{CCPLL}
		Max: $37.5\text{mA} \rightarrow 37\text{mA} (T_A = +105^{\circ}\text{C})$
		Max: $39\text{mA} \rightarrow 38.5\text{mA} (T_A = +125^{\circ}\text{C})$
		I _{CCMAIN}
		Max: $9\text{mA} \rightarrow 8\text{mA} (T_A = +105^{\circ}\text{C})$
		Max: $10.5 \text{mA} \rightarrow 9.5 \text{mA} (T_A = +125 ^{\circ}\text{C})$
37		I_{CCSUB}
		Max: $6mA \rightarrow 3.3mA (T_A = +105^{\circ}C)$
		Max: 7.5 mA → 4.8 mA ($T_A = +125$ °C)
		Added the Symbol to "Power supply current in Sleep modes"
		I _{CCSRCH} , I _{CCSRCL}
		Changed the Conditions of I _{CCSMAIN} in "Power supply current
		in Sleep modes"
		"SMCR:LPMSS=0" is added
		Changed the Value of "Power supply current in Sleep modes"
		I _{CCSPLL}
		Typ: $10\text{mA} \rightarrow 8.5\text{mA} (T_A = +25^{\circ}\text{C})$ Max: $15\text{mA} \rightarrow 14\text{mA} (T_A = +105^{\circ}\text{C})$
		Max: $16.5\text{mA} \rightarrow 14\text{mA} (T_A = +105 \text{ C})$ Max: $16.5\text{mA} \rightarrow 15.5\text{mA} (T_A = +125^{\circ}\text{C})$
		Iccsmain
		Max: $7\text{mA} \rightarrow 4.5\text{m A} (T_A = +105^{\circ}\text{C})$
		$Max: 8.5mA \rightarrow 6mA (T_A = +125^{\circ}C)$
		I_{CCSSUB}
		Typ: $0.08\text{mA} \rightarrow 0.04\text{m A} (T_A = +25^{\circ}\text{C})$
		Max: $4\text{mA} \rightarrow 2.5\text{m A} (T_A = +105^{\circ}\text{C})$
		$Max: 5.5mA \rightarrow 4mA (T_A = +125^{\circ}C)$

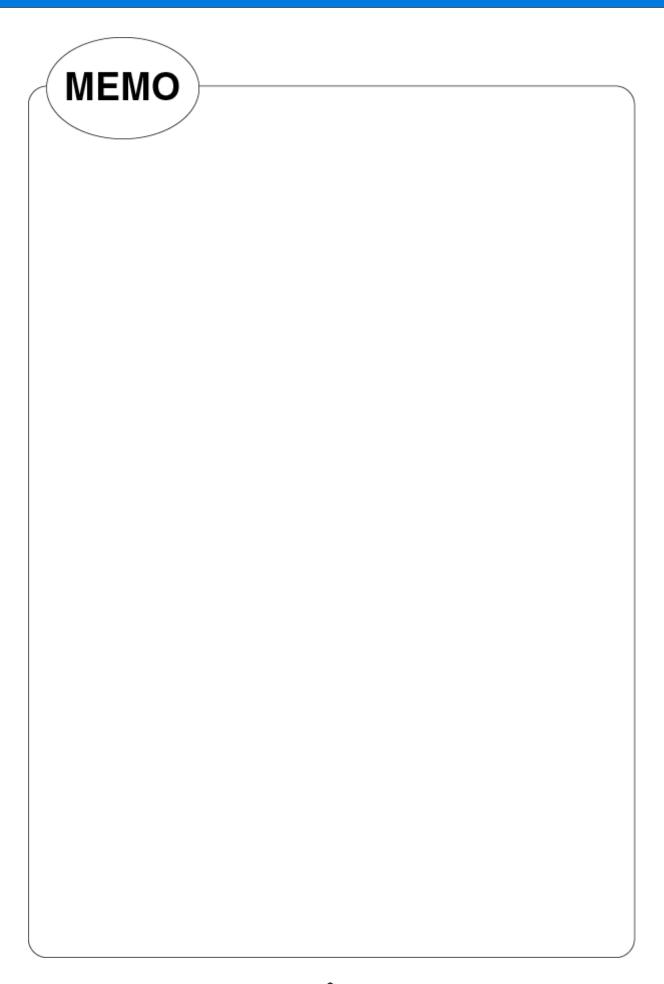
Added the Symbol to "Power supply current in Timer mod l _{CCTPLA} . Changed the Conditions of I _{CCTMAIN} . I _{CCTRCH} in "Power supcurrent in Timer modes" "SMCR:I_PMSS=0" is added Changed the Value of "Power supply current in Timer mod I _{CCTMAIN} Max: 335µA → 330µA (T _A = +25°C) Max: 1300µA → 1195µA (T _A = +105°C) Max: 2310µA → 2165µA (T _A = +125°C) I _{CCTRCH} Max: 245µA → 215µA (T _A = +25°C) Max: 2215µA → 2075µA (T _A = +125°C) Max: 2215µA → 275µA (T _A = +25°C) Max: 1010µA → 905µA (T _A = +105°C) Max: 2015µA → 1880µA (T _A = +105°C) Max: 90µA → 65µA (T _A = +25°C) Max: 90µA → 880µA (T _A = +105°C) Max: 990µA → 1850µA (T _A = +125°C) Changed the Value of "Power supply current in Stop mode I _{CCT} Max: 985µA → 880µA (T _A = +105°C) Max: 985µA → 880µA (T _A = +125°C) Added the Symbol I _{CCTASHPD} Changed the Value and condition of "Power supply current active Low Voltage detector" I _{CCD} I _{CCTASHPD} Changed the Value and condition of "Power supply current active Low Voltage detector" I _{CCD} I _{CCTASHPD} Changed the Value and condition of "Power supply current active Low Voltage detector" I _{CCD} I _{CCTASHPD} Changed the condition of "Flash Write/Erase current" I _{CCTASHPD} Typ: 5µA, Max: -, Remarks: T _A = +25°C Typ: -, Max: 12.5µA, Remarks: T _A = +125°C Changed the annotation *2 Changed the annotation *2 The power supply current is measured with a 4MHz extern clock connected to the Main oscillator and a 32kHz extern clock connected to the Main oscillator and a 32kHz extern clock connected to the Main oscillator and a 32kHz extern clock connected to the Main oscillator and a 32kHz extern clock connected to the Main oscillator and a 32kHz extern clock connected to the Main oscillator and a 32kHz extern clock connected to the Main oscillator and a 32kHz extern clock connected to the Main oscillator and a 32kHz extern clock connected to the Main oscillator and a 32kHz extern clock connected to the Main oscillator and a 32kHz extern clock connected to the Main oscillator and a 32kHz e	Page	Section	Change Results
Changed the Conditions of I _{CCTMAIN} , I _{CCTRCH} in "Power sure current in Timer modes" "SMCR:LPMSS=0" is added Changed the Value of "Power supply current in Timer mod I _{CCTMAIN} Max: 335μA → 330μA (T _A = +25°C) Max: 1300μA → 1195μA (T _A = +105°C) Max: 2310μA → 2165μA (T _A = +125°C) I _{CCTRCH} Max: 245μA → 215μA (T _A = +25°C) Max: 1215μA → 2075μA (T _A = +125°C) I _{CCTRCL} Max: 105μA → 75μA (T _A = +125°C) Max: 1010μA → 905μA (T _A = +125°C) Max: 2015μA → 1880μA (T _A = +125°C) I _{CCTSUB} Max: 99μA → 65μA (T _A = +25°C) Max: 1990μA → 1850μA (T _A = +125°C) Changed the Value of "Power supply current in Stop mode I _{CCT} Max: 985μA → 885μA (T _A = +125°C) Max: 985μA → 60μA (T _A = +25°C) Max: 985μA → 880μA (T _A = +125°C) Added the Value of "Power supply current in Stop mode I _{CCT} Max: 1985μA → 1845μA (T _A = +125°C) Added the Symbol I _{CCTA,SHPD} Changed the Value and condition of "Power supply current active Low Voltage detector" I _{CCLM} I _{CCTM} I _{CCLM} Typ: 5μA, Max: 15μA, Remarks: nothing Typ: 5μA, Max: 15μA, Remarks: T _A = +25°C Typ: ¬Max: 12.5μA, Remarks: T _A = +125°C Changed the condition of "Flash Write/Erase current" I _{CCLM,SH} Typ: 12.5mA, Max: ¬Remarks: T _A = +125°C Changed the condition of "Flash Write/Erase current" I _{CCLM,SH} Typ: 12.5mA, Max: ¬Remarks: T _A = +25°C Typ: ¬Max: 20mA, Remarks: T _A = +25°C Typ: ¬Max: 20mA, Remarks: T _A = +25°C Typ: ¬Max: 20mA, Remarks: T _A = +125°C Changed the annotation *2 The power supply current is measured with a 4MHz extern clock connected to the Main oscillator and a 32kHz extern clock connected to the Main oscillator and a 32kHz extern clock connected to the Main oscillator and a 32kHz extern clock connected to the Main oscillator and a 32kHz extern clock connected to the Main oscillator and a 32kHz extern clock connected to the Main oscillator and a 32kHz extern clock connected to the Main oscillator and a 32kHz extern clock connected to the Main oscillator and a 32kHz extern clock			Added the Symbol to "Power supply current in Timer modes"
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ICCITIAIN Max: 355μ A → 330μ A ($T_A = +25^\circ$ C) Max: 1300μ A → 1195μ A ($T_A = +105^\circ$ C) Max: 2310μ A → 2165μ A ($T_A = +125^\circ$ C) ICCITICI Max: 2245μ A → 215μ A ($T_A = +225^\circ$ C) Max: 1215μ A → 1095μ A ($T_A = +125^\circ$ C) Max: 1215μ A → 1095μ A ($T_A = +125^\circ$ C) Max: 1215μ A → 2075μ A ($T_A = +125^\circ$ C) ICCITICI Max: 105μ A → 75μ A ($T_A = +25^\circ$ C) Max: 1010μ A → 905μ A ($T_A = +105^\circ$ C) Max: 2015μ A → 1880μ A ($T_A = +125^\circ$ C) ICCITSUB Max: 900μ A → 65μ A ($T_A = +125^\circ$ C) Max: 985μ A → 885μ A ($T_A = +125^\circ$ C) Max: 990μ A → 60μ A ($T_A = +125^\circ$ C) Changed the Value of "Power supply current in Stop mode l _{CCH} Max: 90μ A → 60μ A ($T_A = +125^\circ$ C) Max: 985μ A → 880μ A ($T_A = +125^\circ$ C) Max: 985μ A → 880μ A ($T_A = +125^\circ$ C) Added the Symbol l _{CCHASHPO} Changed the Value and condition of "Power supply current active Low Voltage detector" ICCLVD Typ: 5μ A, Max: 15μ A, Remarks: nothing → Typ: 5μ A, Max: $-$, Remarks: $T_A = +25^\circ$ C Typ: $-$, Max: 12.5μ A, Remarks: $T_A = +25^\circ$ C Typ: $-$, Max: 12.5μ A, Remarks: $T_A = +125^\circ$ C Changed the condition of "Flash Write/Erase current" l _{CCHASH} Typ: $12.5m$ A, Max: $-$, Remarks: $T_A = +25^\circ$ C Typ: $-$, Max: $20m$ A, Remarks: $T_A = +25^\circ$ C Typ: $-$, Max: $-$ 0mA, Remarks: $-$ 0mA, Remarks: $-$ 0mA; $-$ 10mA; $-$ 20mA, Remarks: $-$ 10mA; $-$ 20mA, Remarks: $-$ 10mA; $-$ 20mA, Remarks: $-$ 20mA, Remarks: $-$ 20mA, Remarks: $-$ 20mA, Remarks: $-$ 30mA and a 32kHz extern clock connected to the Main oscillator and a 32kHz extern clock connected to the Main oscillator and a 32kHz extern clock connected to the Main oscillator and a 32kHz extern clock connected to the Main oscillator and a 32kHz extern clock connected to the Main oscillator and a 32kHz extern			
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Max: $245\mu A \rightarrow 215\mu A$ ($T_A = +25^{\circ}C$) Max: $1215\mu A \rightarrow 1095\mu A$ ($T_A = +105^{\circ}C$) Max: $2215\mu A \rightarrow 2075\mu A$ ($T_A = +105^{\circ}C$) Max: $105\mu A \rightarrow 2075\mu A$ ($T_A = +125^{\circ}C$) Max: $105\mu A \rightarrow 75\mu A$ ($T_A = +25^{\circ}C$) Max: $1010\mu A \rightarrow 905\mu A$ ($T_A = +105^{\circ}C$) Max: $2015\mu A \rightarrow 1880\mu A$ ($T_A = +125^{\circ}C$) Max: $900\mu A \rightarrow 65\mu A$ ($T_A = +25^{\circ}C$) Max: $990\mu A \rightarrow 65\mu A$ ($T_A = +25^{\circ}C$) Max: $990\mu A \rightarrow 1850\mu A$ ($T_A = +125^{\circ}C$) Max: $990\mu A \rightarrow 1850\mu A$ ($T_A = +125^{\circ}C$) Changed the Value of "Power supply current in Stop mode I_{CCH} Max: $90\mu A \rightarrow 60\mu A$ ($T_A = +25^{\circ}C$) Max: $985\mu A \rightarrow 880\mu A$ ($T_A = +125^{\circ}C$) Max: $985\mu A \rightarrow 880\mu A$ ($T_A = +125^{\circ}C$) Added the Symbol $I_{CCHASHPO}$ Changed the Value and condition of "Power supply current active Low Voltage detector" $I_{CCHASHPO}$ Typ: $5\mu A$, Max: $15\mu A$, Remarks: nothing \rightarrow Typ: $5\mu A$, Max: $-$, Remarks: $T_A = +25^{\circ}C$ Typ: $-$, Max: $12.5\mu A$, Remarks: $T_A = +25^{\circ}C$ Typ: $-$, Max: $12.5\mu A$, Remarks: nothing \rightarrow Typ: $12.5mA$, Max: $-$, Remarks: nothing \rightarrow Typ: $12.5mA$, Max: $-$, Remarks: $ -$			Max: $2310\mu A \rightarrow 2165\mu A (T_A = +125^{\circ}C)$
Max: 2215μ A → 2075μ A (T_A = $+125^\circ$ C) I_{CCTECL} Max: 105μ A → 75μ A (T_A = $+25^\circ$ C) Max: 1010μ A → 905μ A (T_A = $+105^\circ$ C) Max: 2015μ A → 1880μ A (T_A = $+125^\circ$ C) ICCTSUB Max: 90μ A → 65μ A (T_A = $+125^\circ$ C) Max: 990μ A → 65μ A (T_A = $+125^\circ$ C) Max: 990μ A → 1850μ A (T_A = $+125^\circ$ C) Changed the Value of "Power supply current in Stop mode I_{CCH} Max: 990μ A → 60μ A (T_A = $+25^\circ$ C) Max: 9985μ A → 880μ A (T_A = $+125^\circ$ C) Max: 9985μ A → 880μ A (T_A = $+125^\circ$ C) Added the Symbol ICCHASHPD Changed the Value and condition of "Power supply current active Low Voltage detector" ICCLYD Typ: 5μ A, Max: 15μ A, Remarks: nothing → 799° E, 999° E, 999° E, 9999° E, 99999° E, $999999999999999999999999999999999999$	38		Max: $245 \mu A \rightarrow 215 \mu A (T_A = +25 ^{\circ}C)$
Icctrct Max: 105μA \rightarrow 75μA ($T_A = \pm 25^{\circ}$ C) Max: 1010μA \rightarrow 905μA ($T_A = \pm 105^{\circ}$ C) Max: 2015μA \rightarrow 1880μA ($T_A = \pm 105^{\circ}$ C) Icctsub Max: 90μA \rightarrow 65μA ($T_A = \pm 105^{\circ}$ C) Max: 985μA \rightarrow 885μA ($T_A = \pm 105^{\circ}$ C) Max: 1990μA \rightarrow 1850μA ($T_A = \pm 125^{\circ}$ C) Changed the Value of "Power supply current in Stop mode Ich Max: 90μA \rightarrow 60μA ($T_A = \pm 25^{\circ}$ C) Max: 985μA \rightarrow 880μA ($T_A = \pm 105^{\circ}$ C) Max: 985μA \rightarrow 880μA ($T_A = \pm 105^{\circ}$ C) Max: 985μA \rightarrow 880μA ($T_A = \pm 105^{\circ}$ C) Added the Symbol Iccelashed Changed the Value and condition of "Power supply current active Low Voltage detector" Icclivd Typ: 5μA, Max: 15μA, Remarks: nothing \rightarrow Typ: 5μA, Max: -, Remarks: $T_A = \pm 25^{\circ}$ C Typ: -, Max: 12.5μA, Remarks: $T_A = \pm 125^{\circ}$ C Changed the condition of "Flash Write/Erase current" Iccelashed Typ: 12.5mA, Max: -, Remarks: $T_A = \pm 25^{\circ}$ C Typ: -, Max: 20mA, Remarks: $T_A = \pm 25^{\circ}$ C Typ: -, Max: 20mA, Remarks: $T_A = \pm 25^{\circ}$ C Typ: -, Max: 20mA, Remarks: $T_A = \pm 25^{\circ}$ C Typ: -, Max: 20mA, Remarks: $T_A = \pm 25^{\circ}$ C Typ: -, Max: 20mA, Remarks: $T_A = \pm 25^{\circ}$ C Typ: -, Max: 20mA, Remarks: $T_A = \pm 25^{\circ}$ C Typ: -, Max: 20mA, Remarks: $T_A = \pm 25^{\circ}$ C Typ: -, Max: 20mA, Remarks: $T_A = \pm 25^{\circ}$ C Typ: -, Max: 20mA, Remarks: $T_A = \pm 25^{\circ}$ C Typ: -, Max: 20mA, Remarks: $T_A = \pm 25^{\circ}$ C Typ: -, Max: 20mA, Remarks: $T_A = \pm 25^{\circ}$ C Typ: -, Max: 20mA, Remarks: $T_A = \pm 25^{\circ}$ C Typ: -, Max: 20mA, Remarks: $T_A = \pm 25^{\circ}$ C Typ: -, Max: 20mA, Remarks: $T_A = \pm 25^{\circ}$ C Typ: -, Max: 20mA, Remarks: $T_A = \pm 25^{\circ}$ C			
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$\begin{array}{c} \text{Max: } 90\mu\text{A} \rightarrow 65\mu\text{A} (T_\text{A} = +25^\circ\text{C}) \\ \text{Max: } 985\mu\text{A} \rightarrow 885\mu\text{A} (T_\text{A} = +105^\circ\text{C}) \\ \text{Max: } 1990\mu\text{A} \rightarrow 1850\mu\text{A} (T_\text{A} = +125^\circ\text{C}) \\ \text{Changed the Value of "Power supply current in Stop mode } I_{\text{CCH}} \\ \text{Max: } 90\mu\text{A} \rightarrow 60\mu\text{A} (T_\text{A} = +25^\circ\text{C}) \\ \text{Max: } 985\mu\text{A} \rightarrow 880\mu\text{A} (T_\text{A} = +105^\circ\text{C}) \\ \text{Max: } 1985\mu\text{A} \rightarrow 1845\mu\text{A} (T_\text{A} = +125^\circ\text{C}) \\ \text{Added the Symbol} \\ I_{\text{CCFLASHPD}} \\ \text{Changed the Value and condition of "Power supply current active Low Voltage detector"} \\ I_{\text{CCLVD}} \\ \text{Typ: } 5\mu\text{A}, \text{Max: } 15\mu\text{A}, \text{Remarks: nothing} \\ \rightarrow \\ \text{Typ: } 5\mu\text{A}, \text{Max: } -125^\circ\text{C} \\ \text{Typ: } -12.5\mu\text{A}, \text{Remarks: } T_\text{A} = +25^\circ\text{C} \\ \text{Typ: } 12.5\mu\text{A}, \text{Max: } 20\mu\text{A}, \text{Remarks: nothing} \\ \rightarrow \\ \text{Typ: } 12.5\mu\text{A}, \text{Max: } 20\mu\text{A}, \text{Remarks: nothing} \\ \rightarrow \\ \text{Typ: } 12.5\mu\text{A}, \text{Max: } 20\mu\text{A}, \text{Remarks: } T_\text{A} = +25^\circ\text{C} \\ \text{Typ: } -12.5\mu\text{A}, \text{Max: } 20\mu\text{A}, \text{Remarks: } T_\text{A} = +25^\circ\text{C} \\ \text{Typ: } -12.5\mu\text{A}, \text{Max: } 20\mu\text{A}, \text{Remarks: } T_\text{A} = +25^\circ\text{C} \\ \text{Typ: } -12.5\mu\text{A}, \text{Max: } 20\mu\text{A}, \text{Remarks: } T_\text{A} = +125^\circ\text{C} \\ \text{Changed the annotation } *2 \\ \text{The power supply current is measured with a } 4\mu\text{MHz external clock connected to the Main oscillator and a } 32k\text{Hz external clock connected to the Main oscillator and a } 32k\text{Hz external clock connected to the Main oscillator and a } 32k\text{Hz external clock connected to the Main oscillator and a } 32k\text{Hz external clock connected to the Main oscillator and a } 32k\text{Hz external clock connected to the Main oscillator and a } 32k\text{Hz external clock connected to the Main oscillator and a } 32k\text{Hz external clock connected to the Main oscillator and a } 32k\text{Hz external clock connected to } 100000000000000000000000000000000000$			
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The power supply current is measured with a 4MHz extern clock connected to the Main oscillator and a 32kHz externs			
clock connected to the Main oscillator and a 32kHz externa			The power supply current is measured with a 4MHz external
			clock connected to the Main oscillator and a 32kHz external clock connected to the Sub oscillator.
When Flash is not in Power-down / reset mode, I _{CCFLASHPD} must be added to the Power supply current.			When Flash is not in Power-down / reset mode, $I_{\text{CCFLASHPD}}$
The power supply current is measured with a 4MHz extern clock connected to the Main oscillator and a 32kHz externs			The power supply current is measured with a 4MHz external clock connected to the Main oscillator and a 32kHz external clock connected to the Sub oscillator. The current for "On Chip

Page	Section	Change Results
40	3. DC Characteristics (2) Pin Characteristics	Added the Symbol for DEBUG I/F pin $V_{\rm OLD}$
41		Changed the Pin name of "Input capacitance" Other than Vcc, Vss, AVcc, AVss, AVRH → Other than C, Vcc, Vss, AVcc, AVss, AVRH Deleted the annotation "I _{OH} and I _{OL} are target value."
42	4. AC Characteristics (1) Main Clock Input Characteristics	Changed MAX frequency for f $_{FCI}$ in all conditions $16 \rightarrow 8$ Changed MIN frequency for t_{CYLH} $62.5 \rightarrow 125$ Changed MIN, MAX and Unit for P_{WH} , P_{WL} MIN: $30 \rightarrow 55$ MAX: $70 \rightarrow -$ Unit: $\% \rightarrow ns$ Added the figure (t_{CYLH}) when using the external clock
43	4. AC Characteristics (2) Sub Clock Input	Added the figure (t_{CYLL}) when using the crystal oscillator clock
44	Characteristics 4. AC Characteristics (3) Built-in RC Oscillation Characteristics	Added "RC clock stabilization time"
45	4. AC Characteristics (5) Operating Conditions of PLL	Changed the Value of "PLL input clock frequency" Max: $16\text{MHz} \rightarrow 8\text{MHz}$ Changed the Symbol of "PLL oscillation clock frequency" $f_{\text{PLLO}} \rightarrow f_{\text{CLKVCO}}$ Added Remarks to "PLL oscillation clock frequency" Added "PLL phase jitter" and the figure
	4. AC Characteristics (6) Reset Input	Added the figure for reset input time (t _{RSTL})
47	4. AC Characteristics (8) USART Timing	Changed the condition (Vcc = AVcc = 2.7V to 5.5V, Vss = AVss = 0V, Ta = -40°C to + 105°C) \rightarrow (V _{CC} = AV _{CC} = 2.7V to 5.5V, V _{SS} = AV _{SS} = 0V, T _A = -40°C to + 125°C, C _L =50pF) Changed the HARDWARE MANUAL "MB96630 series HARDWARE MANUAL" \rightarrow "MB96600 series HARDWARE MANUAL"
48	1 + 0 01	Changed the figure for "Internal shift clock mode"
50	4. AC Characteristics (10) I ² C timing	Added parameter, "Noise filter" and an annotation *5 for it Added t_{SP} to the figure

S. AD Converter (1) Electrical Characteristics for the AD Converter (2) Accuracy and Setting of the AD Converter (3) Definition of AD Converter (4) Devention of the line between the growth of the figure (5) Low Converter Standard Converter (6) Deviation of the line between the zero-transition point (0500000000000000000000000000000000000	Page	Section	Change Results
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the A/D Converter 5. A/D Converter 5. A/D Converter Sampling Time 5. A/D Converter (3) Definition of A/D Converter Terms 5. A/D Converter (3) Definition of A/D Converter Terms Changed the Description and the figure "Linearity" → "Nonlinearity" "Differential Innearity error" Changed the Description and the fugure "Linearity error" Deviation of the line between the zero-transition point (0b00000000000000000000000000000000000	51		
S. A/D Converter (2) Accuracy and Setting of the A/D Converter Sampling Time			
Sampling time Sampling Time			
SAD Converter Sampling Time 5. A/D Converter (3) Definition of A/D Converter Terms Changed the Description and the figure "Linearity" → "Nonlinearity" "Differential linearity error" Changed the Description Linearity error: Deviation of the line between the zero-transition point (0b0000000000—0b0000000001) and the full-scale transition point (0b111111110) ← 0b1111111111) from the actual conversion characteristics. → Nonlinearity error: Deviation of the actual conversion characteristics from a straight line that connects the zero transition point (0b0000000000 ← 0b0000000001) to the full-scale transition point (0b111111111) ← 0b1111111111). Added the Description "Zero transition voltage" Full scale transition voltage" Added the Value of "Power supply voltage change rate" Max: +0.004 V/µs Added "Pstercis width" (V _{HYS}) Added "Pstercis width" (V _{HYS}) Added "Pstercis width" (V _{HYS}) Added "Betection delay time" (t _d) Deleted the Remarks Added the figure for "Hysteresis width" Added the figure for "Hysteresis width" Added the figure for "Stabilization time" Changed the Value of "Sector erase time" Changed the Parameter "Half word (16-bit) write time" Changed the Value of "Sector erase time" Changed the Value of "Chip erase time" Changed the Remarks of "Sector erase time" Changed the Remarks of "Sector erase time" Changed the Parameter "Half word (16-bit) write time" Changed the Note and annotation *1 Deleted "(targeted value)" from title "Write/Erase cycles and data hold time" Excludes write time prior to internal erase Added the Note and annotation *1	52		==
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Page	Section	Change Results
61	■ORDERING INFORMATION	Changed part number • MCU with CAN controller MB96F636RAPMC-GSE1* → MB96F636RBPMC-GSE1 MB96F636RAPMC-GSE2* → MB96F636RBPMC-GSE2 MB96F637RAPMC-GSE1* → MB96F637RBPMC-GSE1 MB96F637RAPMC-GSE2* → MB96F637RBPMC-GSE2
61	■ORDERING INFORMATION	Added part number • MCU with CAN controller MB96F633RBPMC-GSE1 MB96F635RBPMC-GSE2 MB96F635RBPMC-GSE1 MB96F635RBPMC-GSE2 • MCU without CAN controller MB96F633ABPMC-GSE1 MB96F633ABPMC-GSE1 MB96F635ABPMC-GSE2 MB96F635ABPMC-GSE1 MB96F635ABPMC-GSE1





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Edited: Sales Promotion Department